

Electrosynthesis of nanostructures for energy

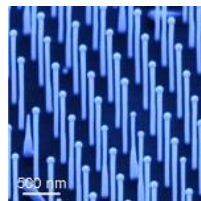
N. STEIN

Electrochemistry of Materials Research Group

thematic school of the GDR NAME

ELaboration of NANOmaterials for the recovery, conversion, transport and storage of energy

11-16 June 2023

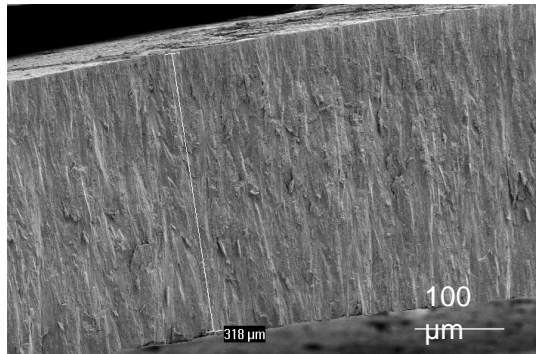


N A M E

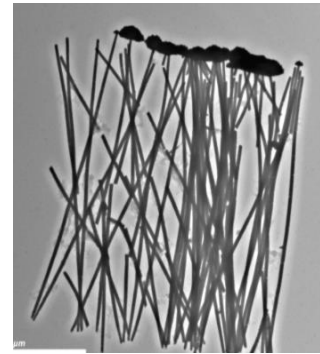
GDR NANoMaterials for Energy applications

Electrochemistry of Materials Research group: *Scientific objectives*

- Analytic study of chemical and electrochemical systems for optimized processes
- **Synthesis and processing of functional materials by electrolysis ...**



Electroplated thick film of bismuth telluride for Peltier modules



Bundle of electroplated Bismuth telluride nanowires

Thermoelectric materials

Contents

1. Electrosynthesis of films
 - a) Basics
 - b) Example : Bismuth Telluride
2. The synthesis of nanostructures by electrosynthesis
 - a) Low dimensional films (2D)
 - b) Focus on the 1D nanostructures

Contents

1. Electrosynthesis of films

a) Basics

b) Example : Bismuth Telluride

2. The synthesis of nanostructures by electrosynthesis

a) Low dimensional films (2D)

b) Focus on the 1D nanostructures

Basics of electrosynthesis

Electrosynthesis :



WIKIPEDIA
The Free Encyclopedia

« *synthesis of chemical compounds in an electrochemical cell* »

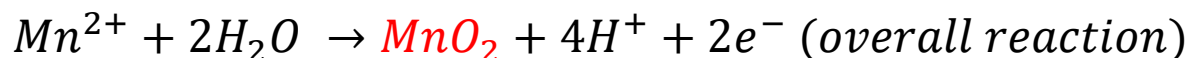
Products of the reaction on the electrode = **electrodeposition**

➤ **direct reduction** of chemical compound at an electrode assisted by external electrical source

➤ **Cathodic reaction** : $Cu^{2+} + 2e^{-} \rightarrow Cu^{\circ}$

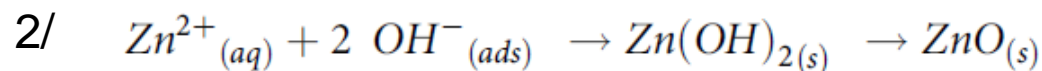
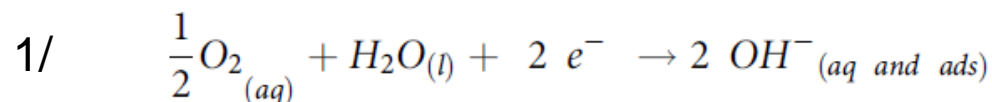
➤ **direct oxidation** of chemical compound at an electrode assisted by external electrical source

➤ **Anodic reaction** : synthesis of manganese dioxide



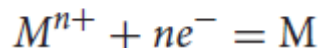
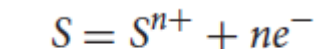
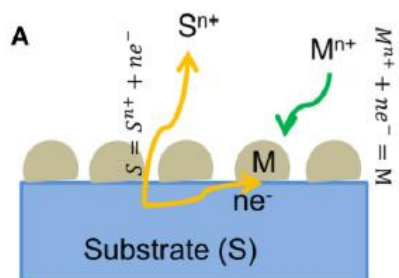
Basics of electrosynthesis

- **Indirect synthesis** induced by anodic or cathodic reaction assisted by external electrical source



- **from a chemical reductor** (electroless deposition) No external source, more difficulty to control the thickness and uniformity of the deposits

Exposing a less noble metal containing solution (S) to a more noble metal (M)



Galvanic displacement reaction

- Examples : GaSb, Bi₂Te₃...

Basics of electrosynthesis

Experimental setup

Working electrode

Exposed area for the deposition

Reference electrode

Define the thermodynamic voltage $V_{WE} - V_{Ref}$

Counter electrode

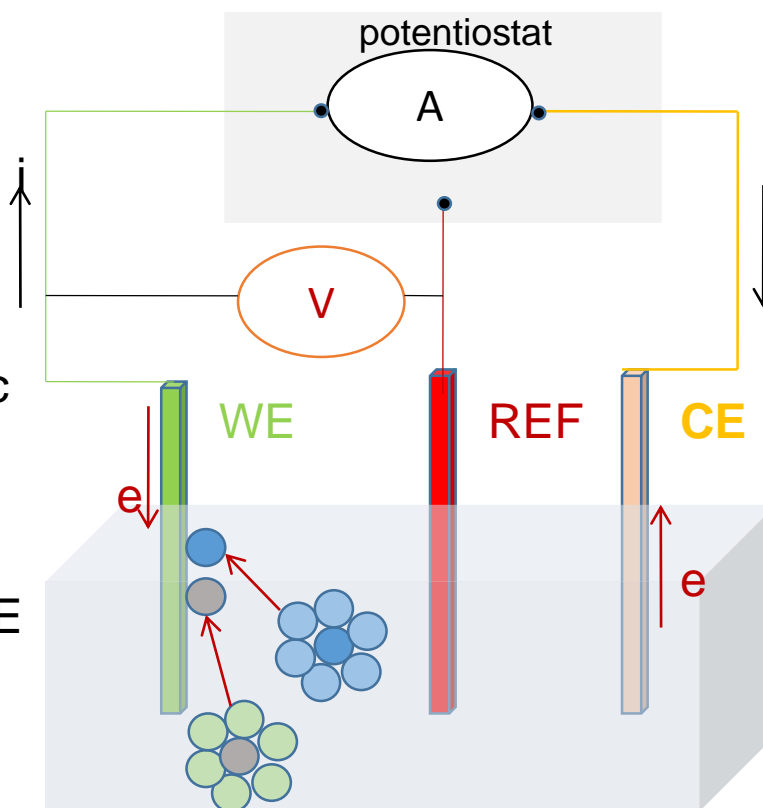
Reverse reaction of the WE

external source

Potentiostat E_{fixed}

Galvanostat I_{fixed}

Waveform generator



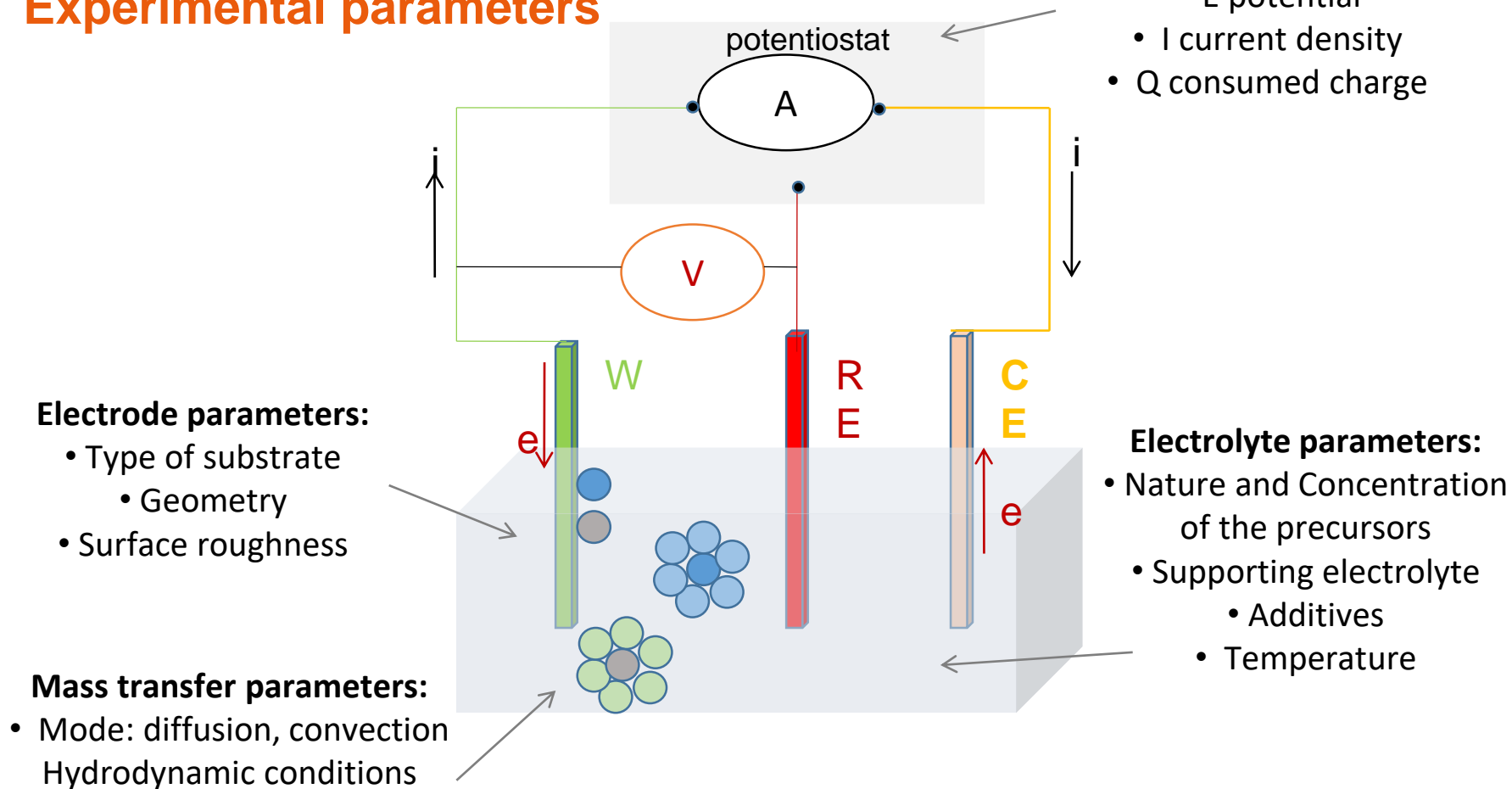
Electrolyte solution

aqueous, non aqueous, ionic liquids, or molten salts



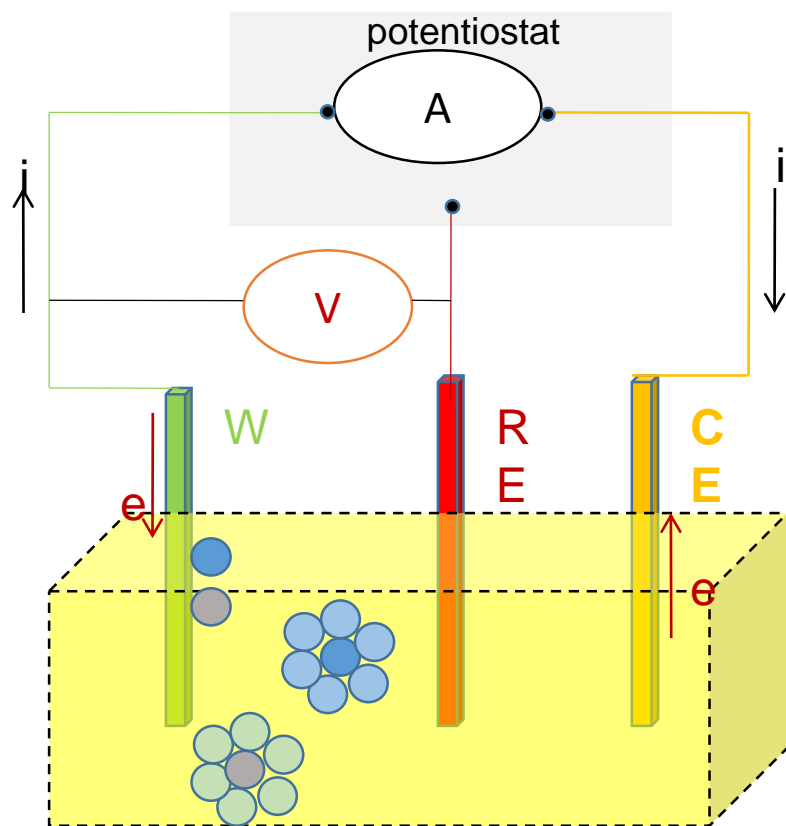
Basics of electrosynthesis

Experimental parameters



Basics of electrosynthesis

Chemical parameters



Type and concentration of precursors
Solubility of the precursors
solvent : aqueous or not aqueous medium
Complexing agents = electrochemistry
additives = morphology
Temperature = mass transport
Viscosity = mass transport

Side reactions
Hydrogen evolution Reaction
electroactivity domain

Basics of electrosynthesis

Chemical parameters : the importance of the electrolyte solution

H	<div><div></div>Electrodeposited metal</div> <div>in aqueous medium</div>																He						
Li	Be	<div>Limitation by hydrogen evolution</div> <div>($E \sim -1.2$ V) $\text{H}_2\text{O} + 1\text{e}^- \rightarrow \frac{1}{2} \text{H}_2 + \text{OH}^-$</div>																B	C	N	O	F	Ne
Na	Mg																	Al	Si	P	S	Cl	Ar
K	Ca	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn	Ga	Ge	As	Se	Br	Kr						
Rb	Sr	Y	Zr	Nb	Mo	Tc	Ru	Rh	Pd	Ag	Cd	In	Sn	Sb	Te	I	Xe						
Cs	Ba	La	Hf	Ta	W	Re	Os	Ir	Pt	Au	Hg	Tl	Pb	Bi	Po	At	Rn						
Fr	Ra	Ac	Rf	Db	Sg	Bh	Hs	Mt	Uun	Uuu	Uub		Uuq										

Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu
Th	Pa	U	Np	Pu	Am	Cm	Bk	Cf	Es	Fm	Md	No	Lr

Reduction reaction	E° (V vs. SHE)
$\text{Mn}^{2+} + 2\text{e}^- \rightarrow \text{Mn}$	-1.19
$\text{Zn}^{2+} + 2\text{e}^- \rightarrow \text{Zn}$	-0.76
$\text{Fe}^{2+} + 2\text{e}^- \rightarrow \text{Fe}$	-0.45
$\text{Co}^{2+} + 2\text{e}^- \rightarrow \text{Co}$	-0.28
$\text{Ni}^{2+} + 2\text{e}^- \rightarrow \text{Ni}$	-0.26
$\text{Cu}^{2+} + 2\text{e}^- \rightarrow \text{Cu}$	+0.34
$\text{Rh}^{3+} + 3\text{e}^- \rightarrow \text{Rh}$	+0.76
$\text{Pd}^{2+} + 2\text{e}^- \rightarrow \text{Pd}$	+0.95
$\text{Ag}^+ + \text{e}^- \rightarrow \text{Ag}$	+0.80
$\text{Ir}^{3+} + 3\text{e}^- \rightarrow \text{Ir}$	+1.16
$\text{Pt}^{2+} + 2\text{e}^- \rightarrow \text{Pt}$	+1.18
$\text{Au}^{3+} + 3\text{e}^- \rightarrow \text{Au}$	+1.50

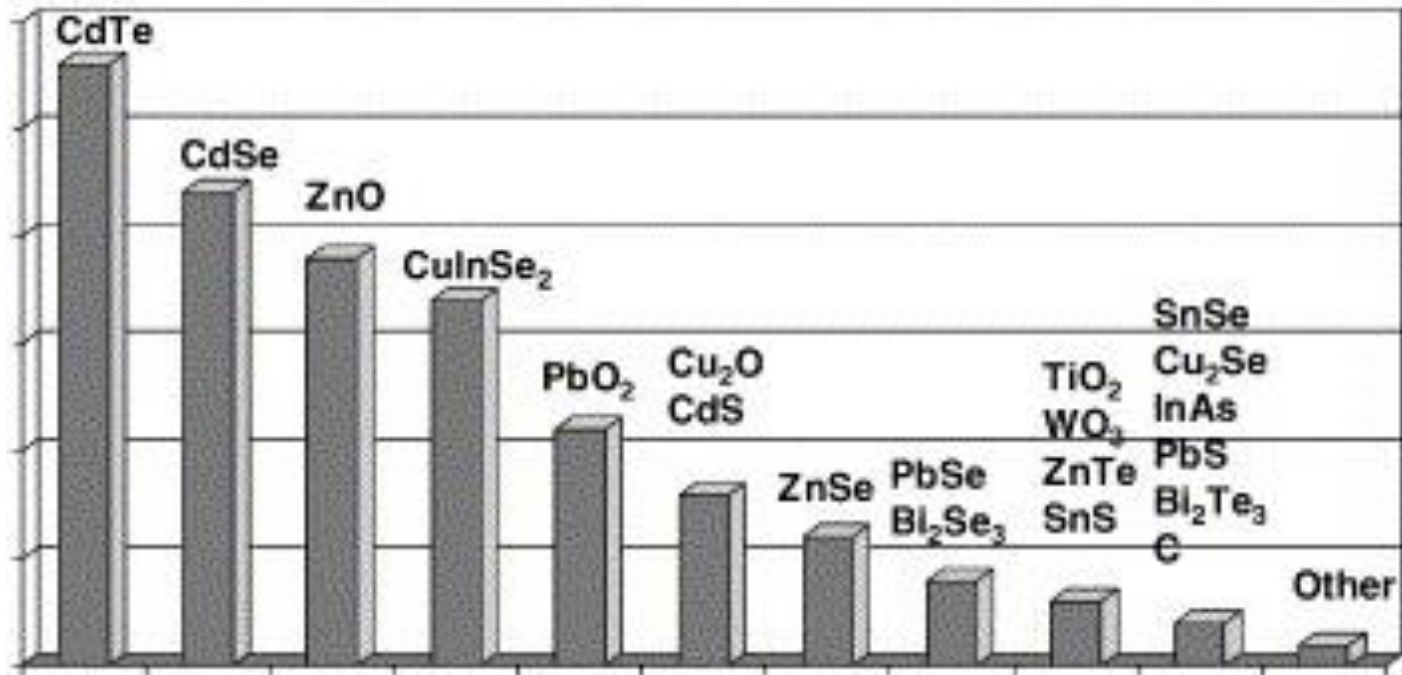
Chemical parameters : the importance of the electrolyte solution



INSTITUT
JEAN LAMOUR

  UNIVERSITÉ
DE LORRAINE

Electrodeposition of semiconductors



Number of published papers from Current Contents data base (2002) as a function of the nature of the semiconductor

Basics of electrosynthesis

Electrical parameters = i current density and Q consumed charge



Reaction speed = v_c

$$v_c = \frac{\partial \xi}{\partial t} = \frac{\partial n_M}{\partial t} = -\frac{1}{n} \frac{\partial n_{e^-}}{\partial t}$$

$$v_c = -\frac{i}{nF} = -\frac{1}{nF} \frac{\partial Q}{\partial t}$$

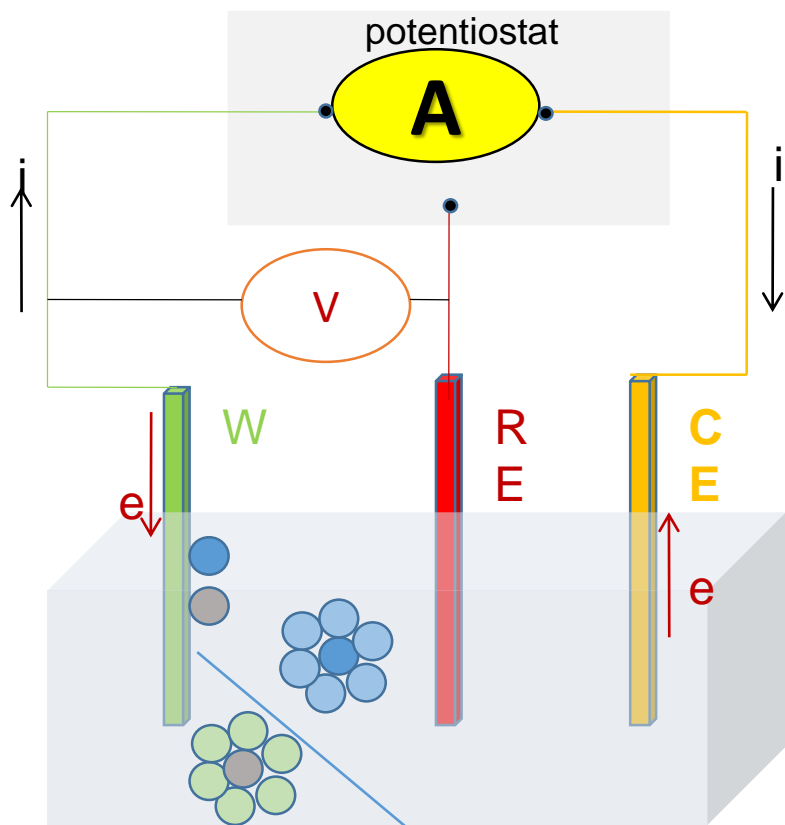
$$Q = \int i dt = n_e F = \frac{m}{M} F = \frac{\rho e A}{M} F$$

Avogadro's constant F

Mass of deposits m

Thickness e

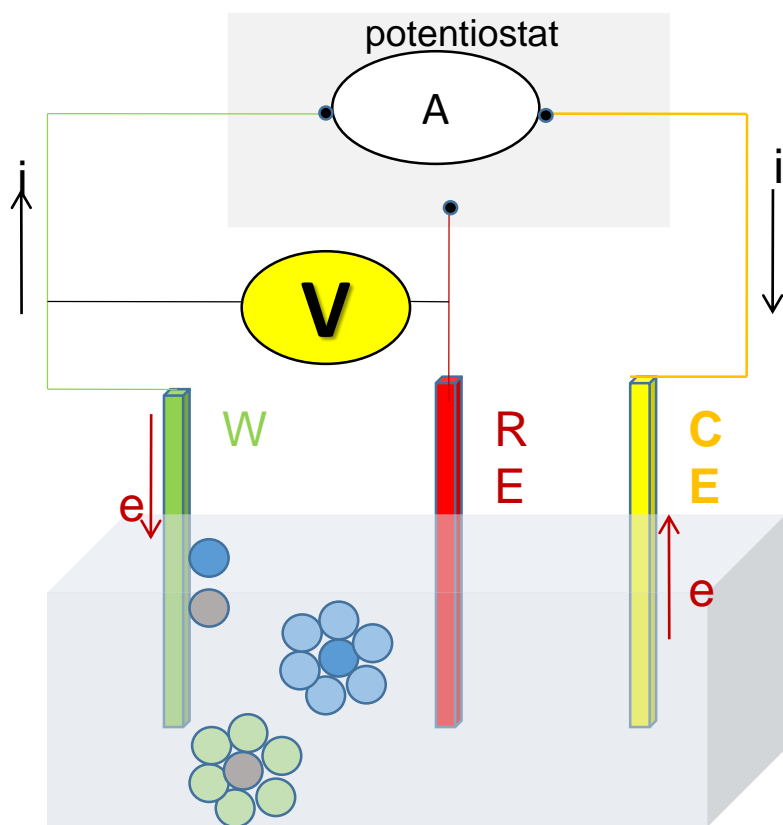
$$\text{Faradic Yield } FY(\%) = \frac{e_{exp}}{e_{th}}$$



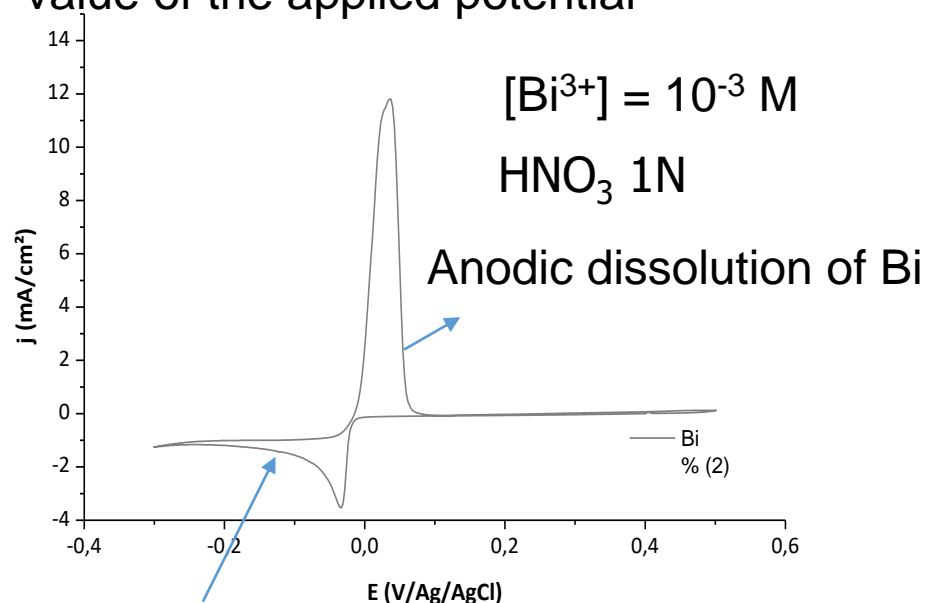
A = Active Area

Basics of electrosynthesis

Electrical parameters : E potential

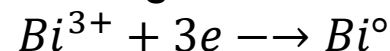


The cyclic voltammetry a tool to define the value of the applied potential



Potential window

Selectivity of the targeted cathodic reaction

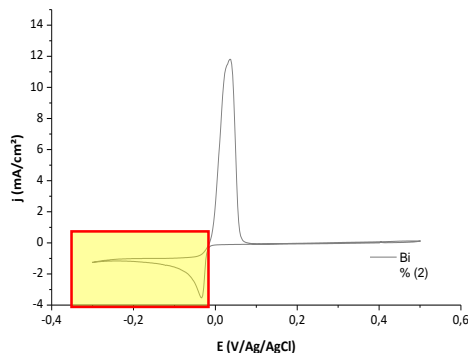


Side reactions

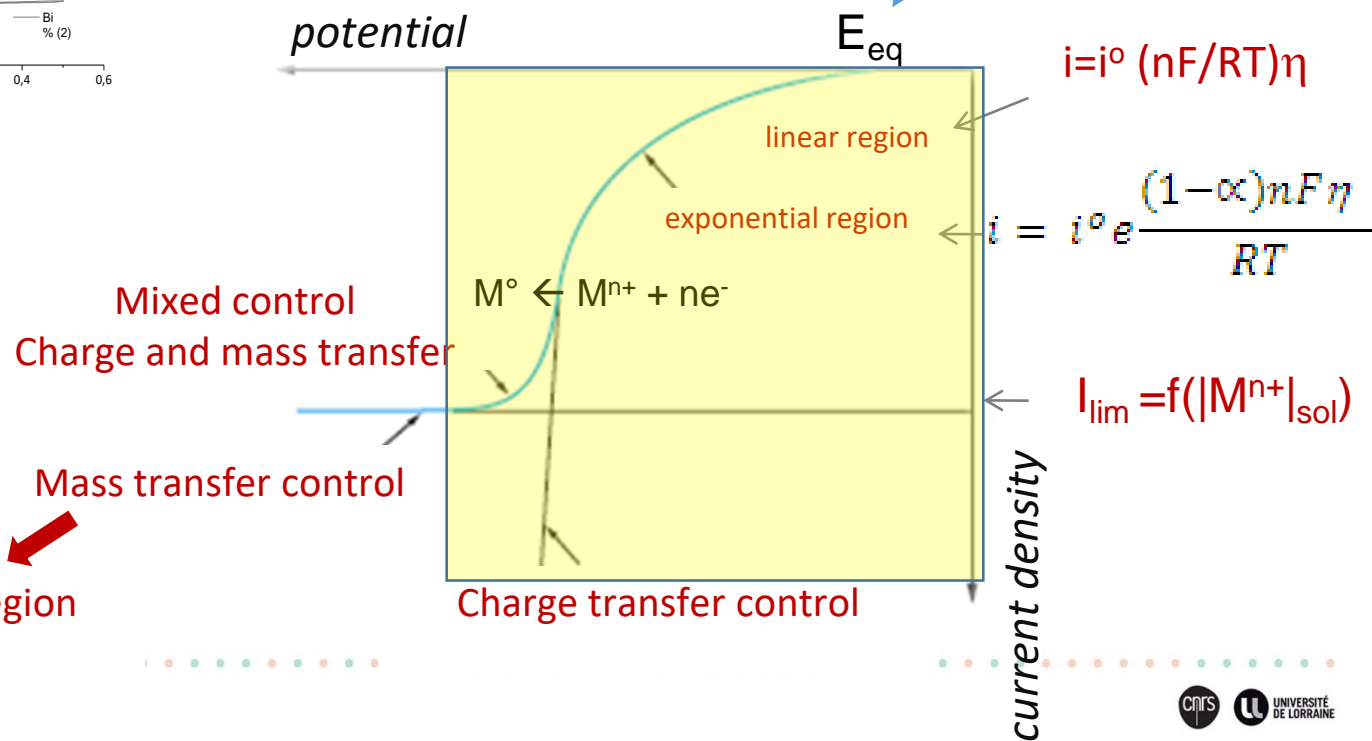
Hydrogen evolution Reaction

Basics of electrosynthesis

Electrical parameters : E potential

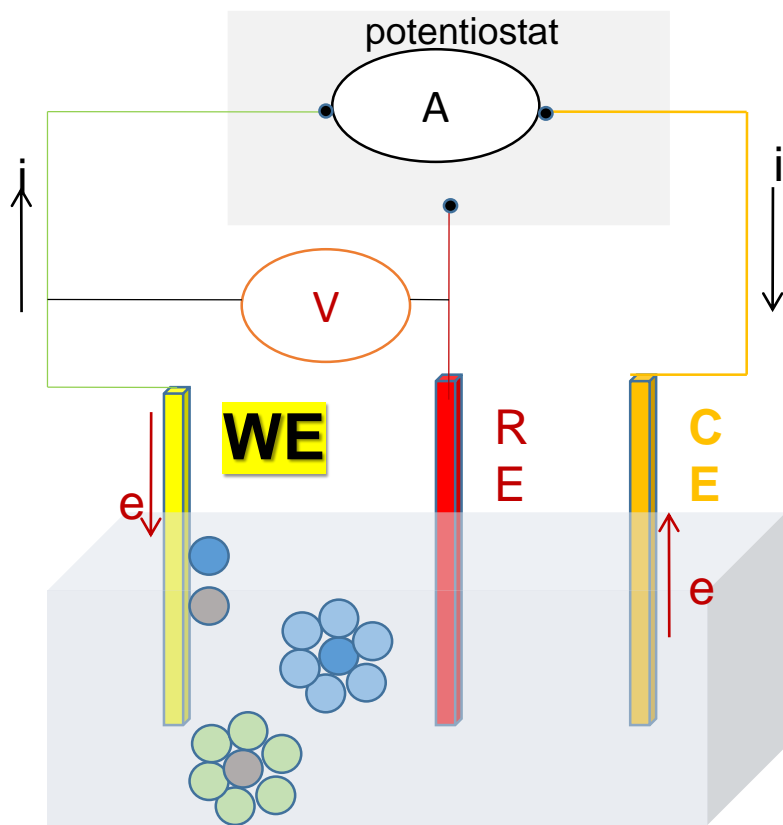


$$E_{eq} = E_{M^{n+}/M^0}^0 + \frac{RT}{nF} \ln \frac{a_{M^{n+}}}{a_{M^0}}$$



Basics of electrosynthesis

Nature of the electrode

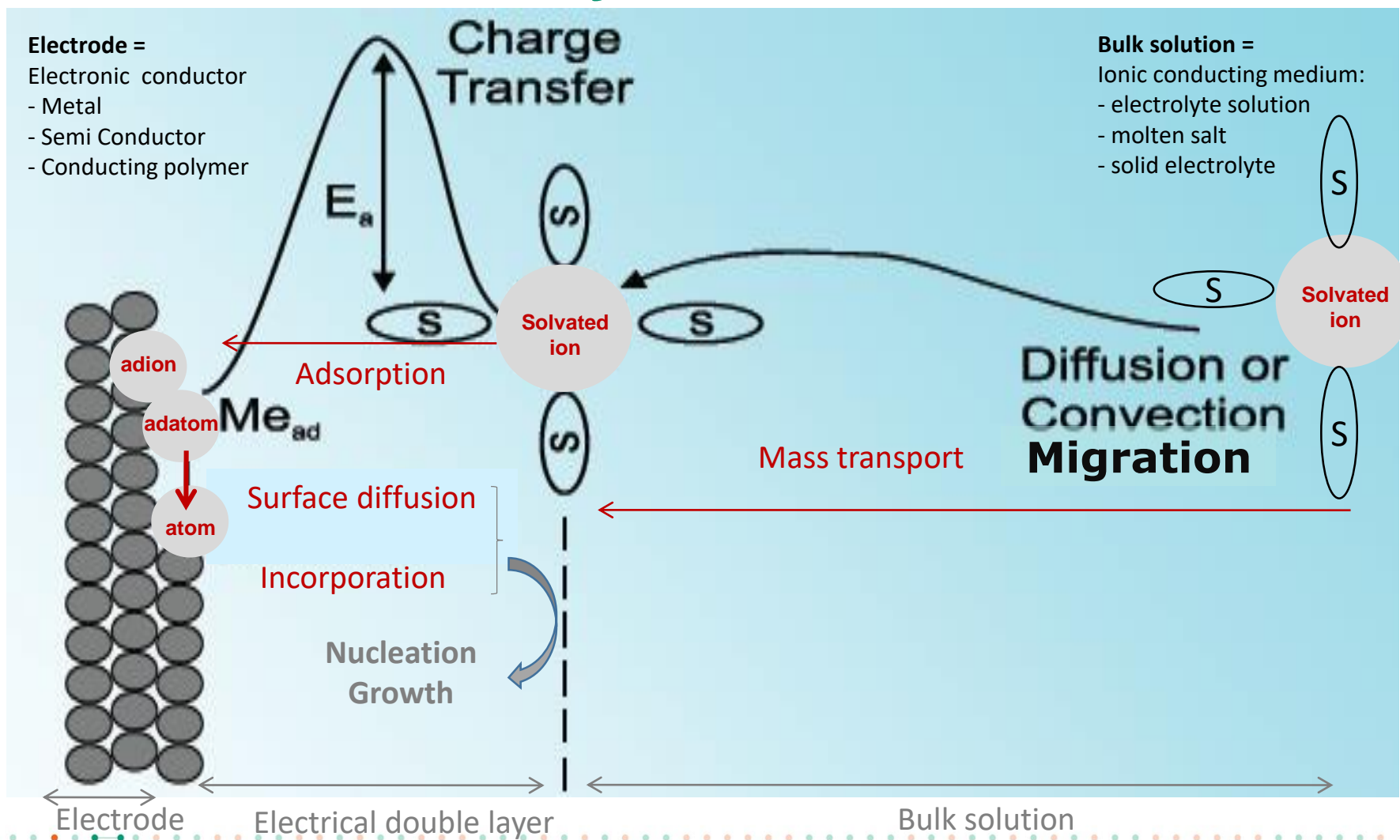


electronic substrate

- Charge transfer
- Geometry
- surface roughness

=> **electrocrystallization process**

Basics of electrosynthesis

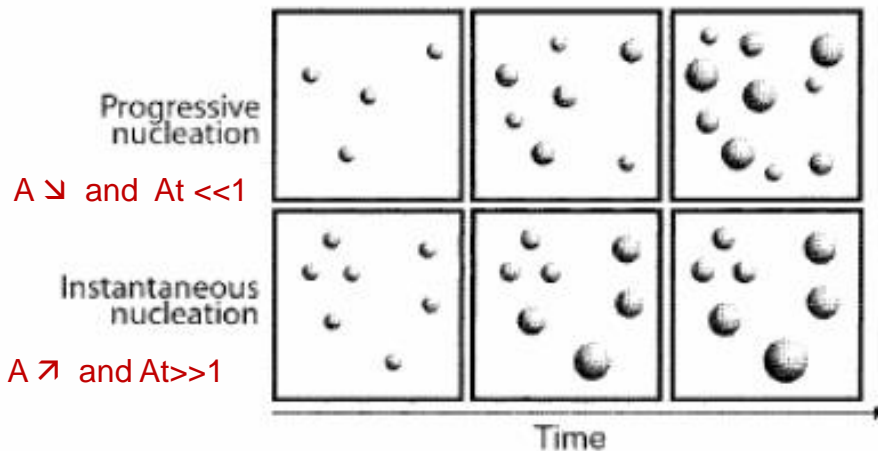


Basics of electrosynthesis

Growth

defects on crystal face → nucleation sites for electrodeposition

SCHEME 1: Generation of a Polydisperse Particle Size Distribution for Electrodeposition Experiments Where Nucleation Is Progressive and Instantaneous



$$N = N_0[1 - \exp(-At)]$$

N_0 = total number of sites
(maximum possible number of nuclei per unit surface)
 A = nucleation rate constant

$$N \approx N_0At$$

increase of nuclei number
during the growth process

$$N \approx N_0$$

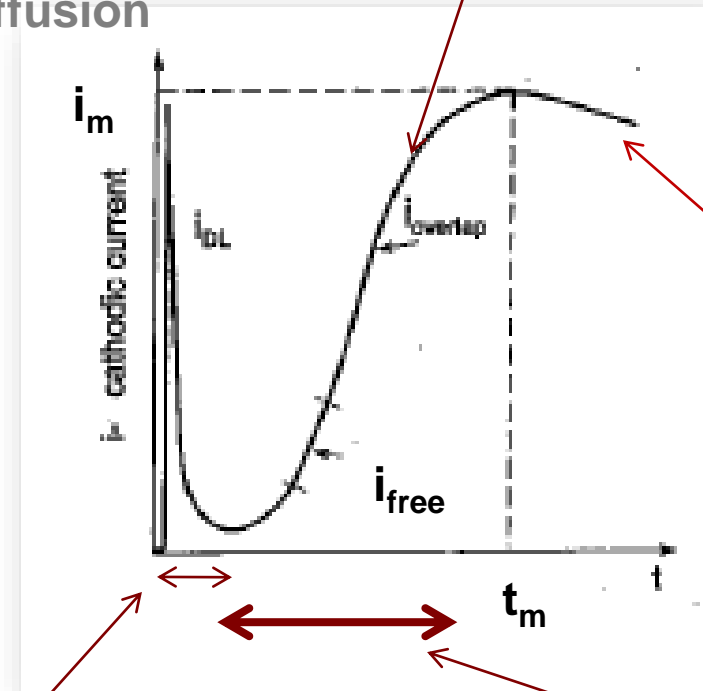
immediate activation of all reaction sites
and constant number of nuclei

Nucleation – growth

Electrochemist point of view

current-time transients $i=f(t)$

Example of 3D nucleation
limited by diffusion



Z_3 = overlap of nuclei

Slowing down of nucleation and current ↘

Z_4 = diffusion of ions in solution
Limiting current

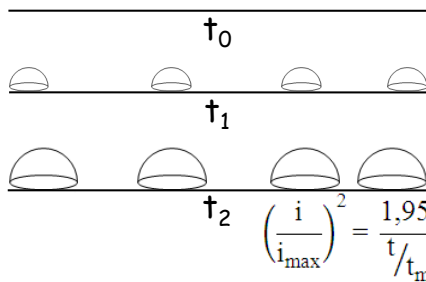
Z_1 = double layer charging
current

$Z_2 = i \nearrow$
- growth of independant nuclei
- increase in nb of nuclei

Current time transients

theoretical models of nucleation

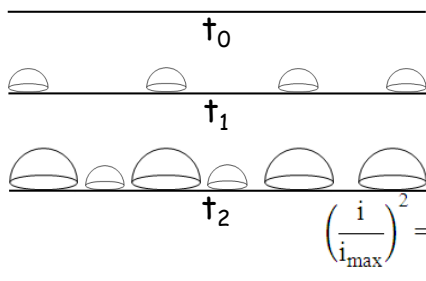
3D Nucleation



Instantaneous nucleation

immediate activation of all reaction sites
and constant number of nuclei

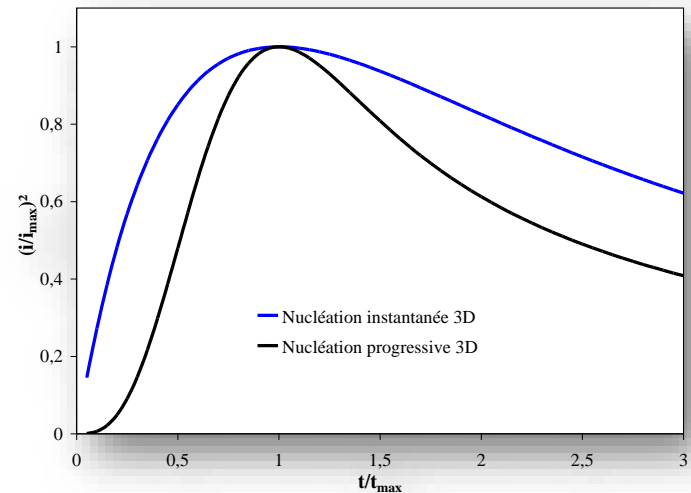
$$\left(\frac{i}{i_{\max}}\right)^2 = \frac{1,9542}{t/t_{\max}} \left(1 - \exp\left[-1,2564 \left(\frac{t}{t_{\max}}\right)\right]\right)^2$$



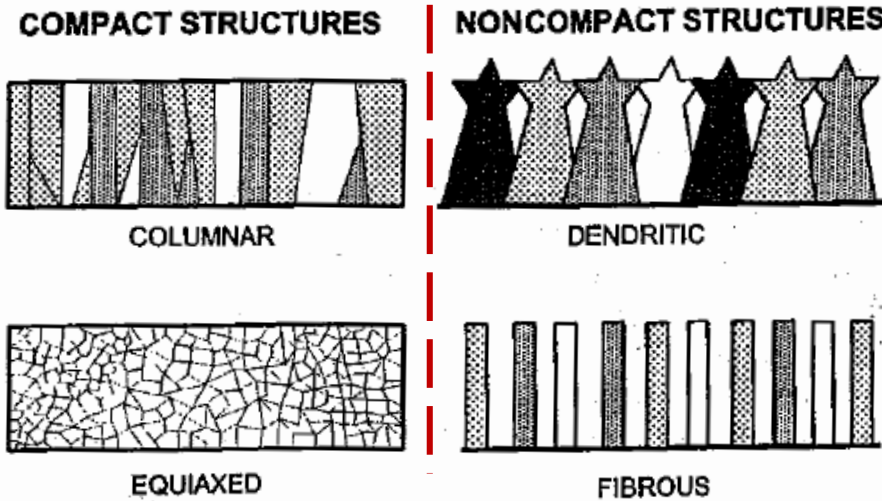
Progressive nucleation

increase of nuclei number during the
growth process

$$\left(\frac{i}{i_{\max}}\right)^2 = \frac{1,2254}{t/t_{\max}} \left(1 - \exp\left[-2,3367 \left(\frac{t}{t_{\max}}\right)^2\right]\right)^2$$



Electrocristallization

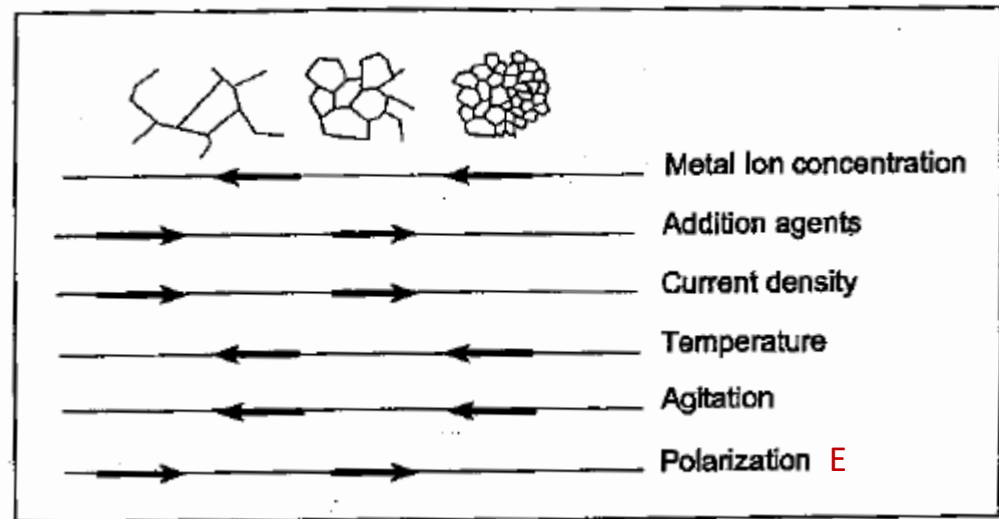


Schematic présentation
of grain structures of electrodeposited films

Operating conditions over electrodeposit structure

Arrow: increase of the given
parameter
in determining grain sizes

- But also
- Chelates
 - Other C^+ et A^-
 - Substrate
 - pH
 - Adsorbed species



Contents

1. Electrosynthesis of films

a) Basics

b) Example : electrodeposition of Bismuth Telluride

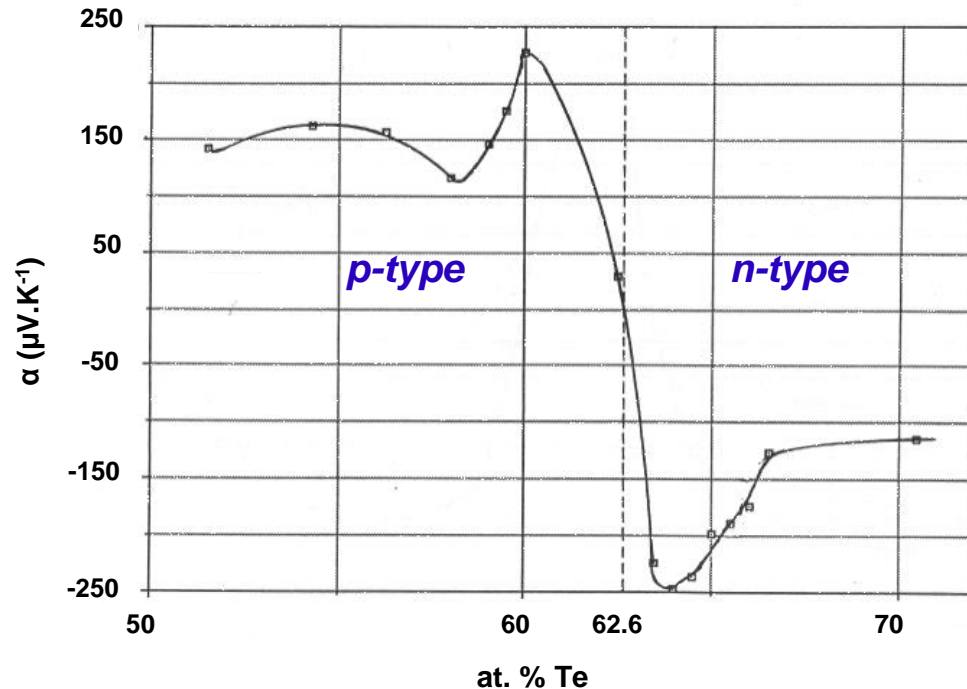
2. The synthesis of nanostructures by electrosynthesis

a) Low dimensional films (2D)

b) Focus on the 1D nanostructures

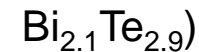
Example : electrodeposition of Bismuth Telluride

Thermoelectric material

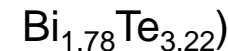


A textbook case !

Bi excess \rightarrow **p-type** ($ZT^{300\text{K}} = 0.54$ for



Te excess \rightarrow **n-type** ($ZT^{300\text{K}} = 0.65$ pour



Conductivity transition : $\text{Bi}_{1.88}\text{Te}_{3.12}$

High dependence of chemical composition on the transport properties of the compound
Necessary to monitor the composition of Bi_2Te_3

Example : electrodeposition of Bismuth Telluride

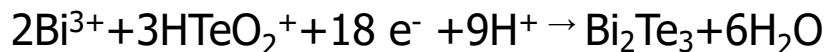
Setting of the electrodeposition setup

Electrolyte solution

HNO₃ 1M

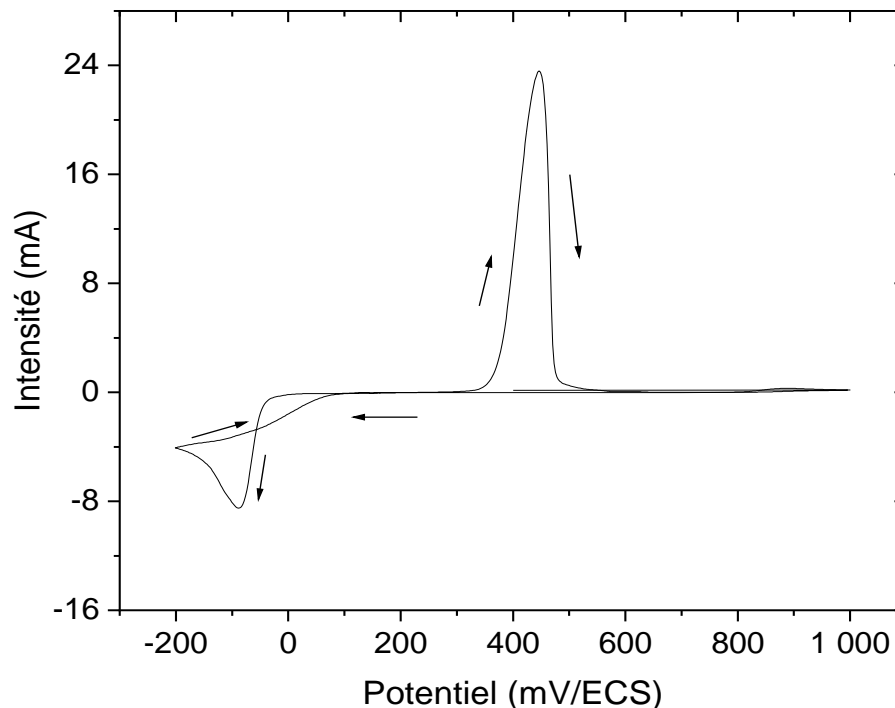
[Bi³⁺]=[HTeO₂⁺] = 10⁻³ M

Cathodic reaction



Mechanism

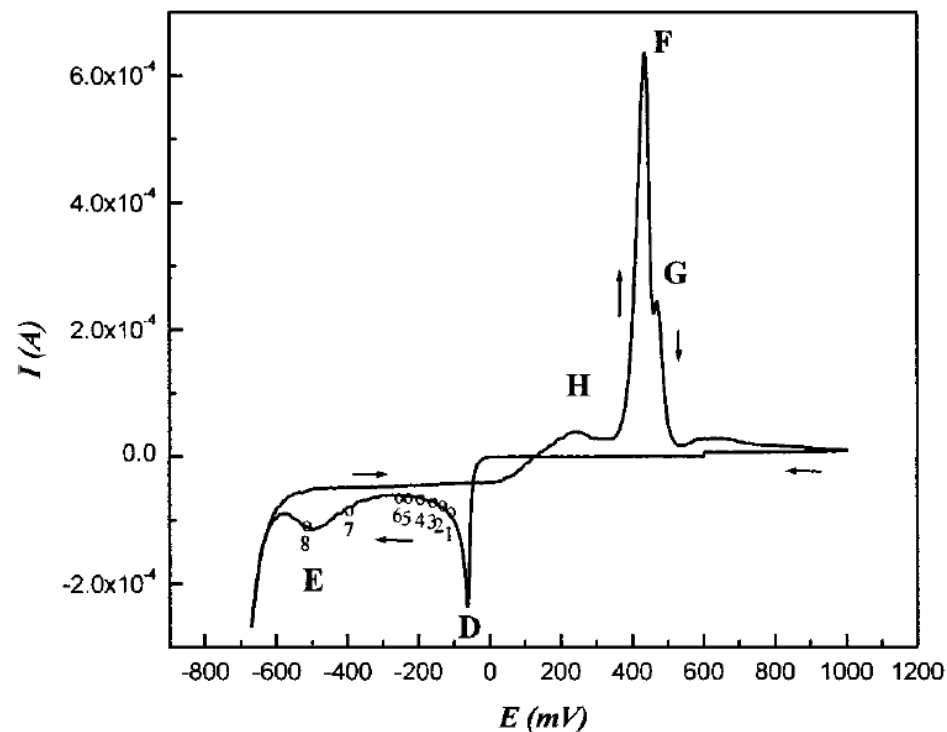
Coreduction or precipitation ?



Single phase in acidic Medium

Example : electrodeposition of Bismuth Telluride

Setting of the electrodeposition setup



Several anodic peaks

=>Bi-Rich deposits at more cathodic potentials
(E peak = Bi reduction)

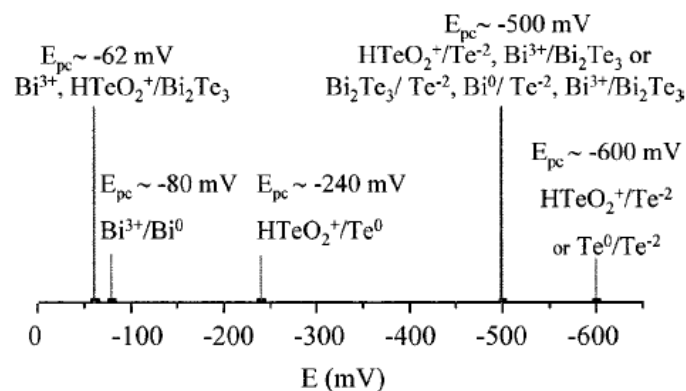
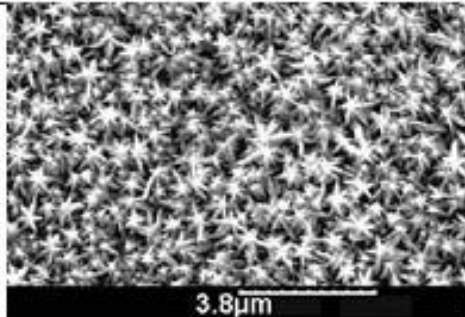


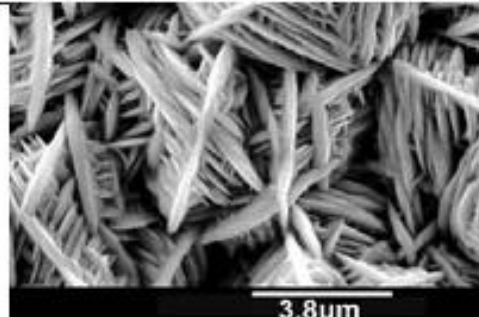
Figure 8. Summary of the reduction potentials observed as determined by the cyclic voltammogram studies.

Example : electrodeposition of Bismuth Telluride

Influence of the applied potential



$E_{\text{deposit}} = -40 \text{ mV/ECS}$



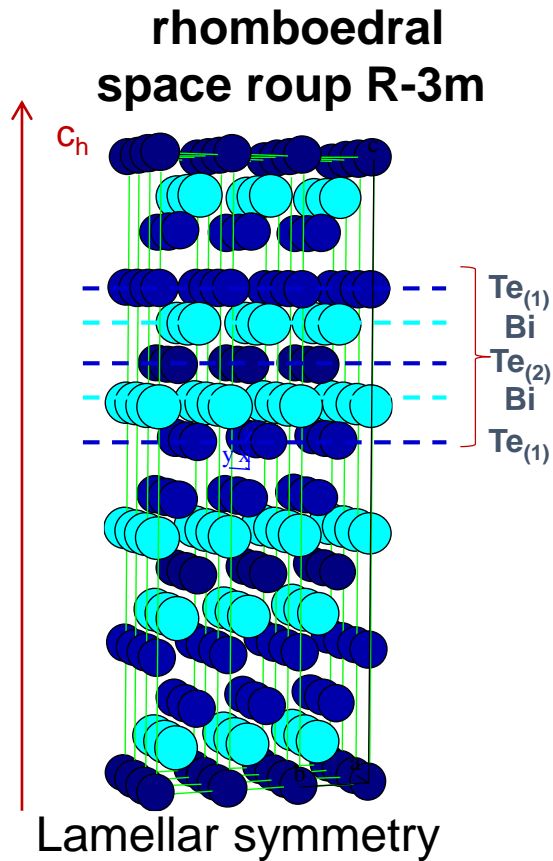
$E_{\text{deposit}} = -100 \text{ mV/ECS}$

at more cathodic applied potentials

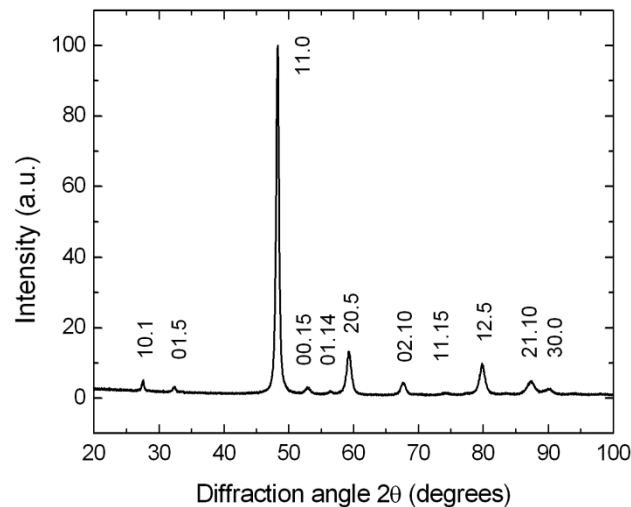
- Bi enrichment
- Coarser grains

Example : electrodeposition of Bismuth Telluride

Influence of the applied potential

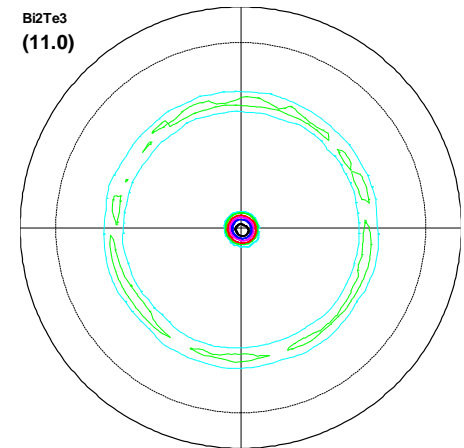


XRD analysis



Preferential growth direction
perpendicular to (110)

Pole figure analysis



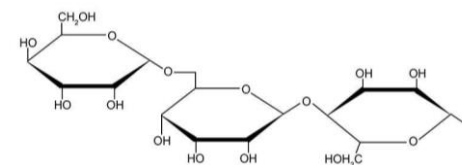
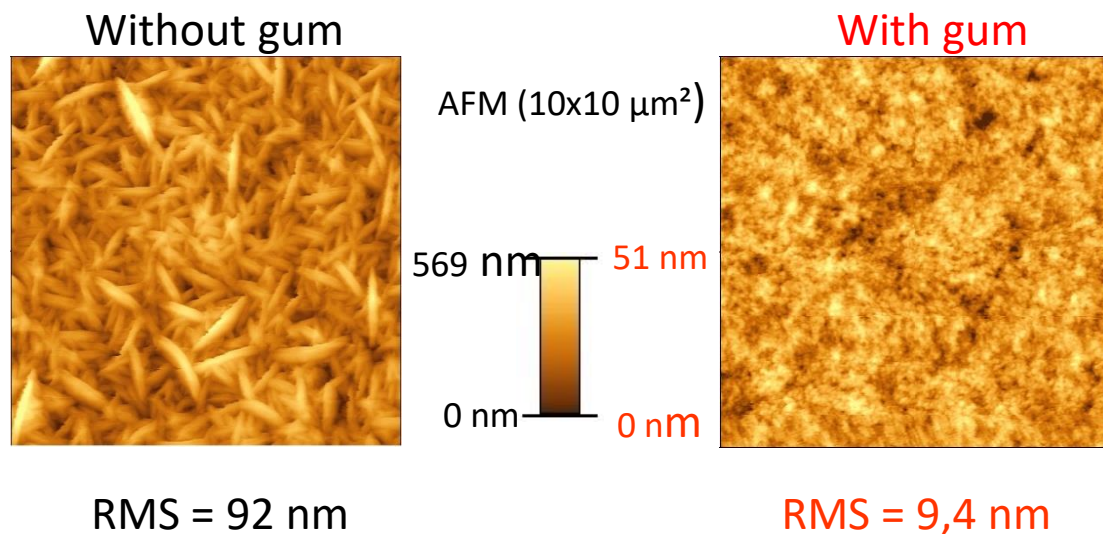
fiber texture

Influence of the applied potential



Example : electrodeposition of Bismuth Telluride

Influence of the additive on the roughness



Arabic gum 0,01 wt. %

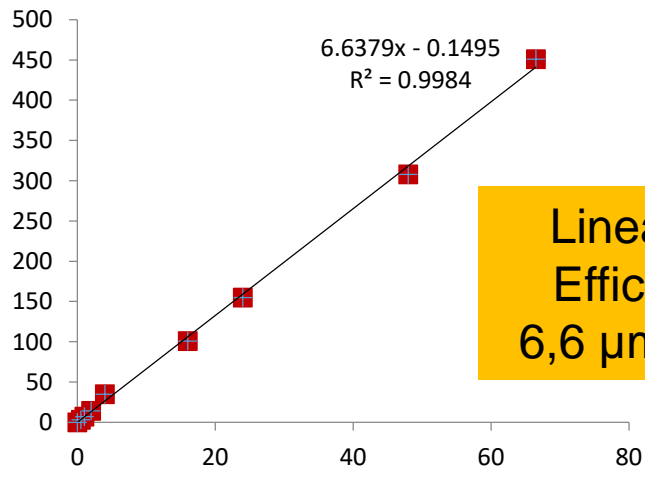
$[Bi]/[Te] = 1$ $[Te] = 10^{-2} M$
 $-0.25 A/dm^2 < J < -0.10 A/dm^2$

	Bi _{1,8} Te _{3,2}	Bi _{2,0} Te _{3,0}	Bi _{2,2} Te _{2,8}
S ($\mu\text{V/K}$) without gum	-75	-65	-50
S ($\mu\text{V/K}$) with Arabic gum	-167	-115	-56

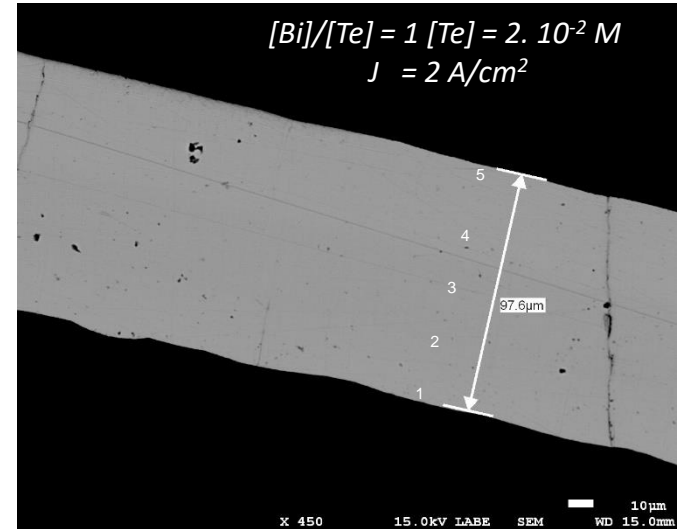
Towards application

- Interest of anode to maintain the concentration of cations in the electrolyte
- No modification of the electrolyte concentration even after 100 h
- Constant stoichiometry = $f(t) = f(\text{thickness})$

Thickness
(μm)



Linear growth rate
Efficiency $\sim 100\%$
 $6,6 \mu\text{m/h} \rightarrow 450 \mu\text{m}$



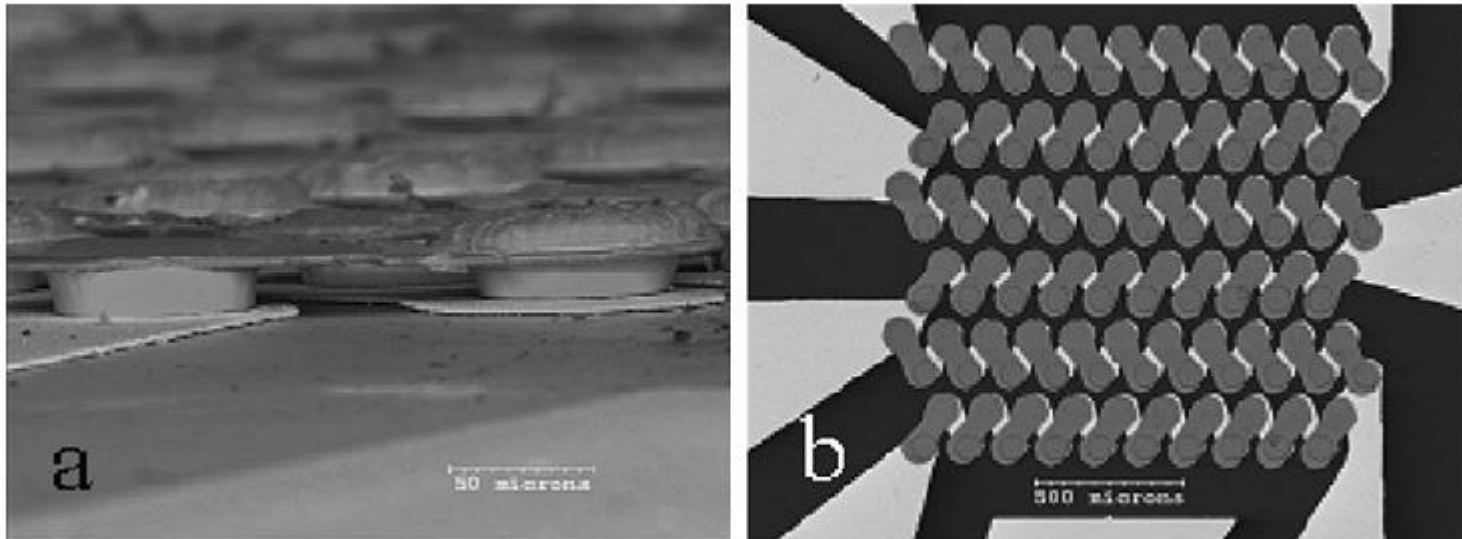
Cross section composition
for one film:

1 : 37,96%Bi ; 62,04%Te
2 : 38,00%Bi ; 62,00 %Te
3 : 36,58%Bi ; 63,42%Te
4 : 37,83%Bi ; 62,17%Te
5 : 37,58%Bi ; 62,43%Te

average : 37,38%Bi ; 62,62%Te
 $\pm 0,82$

Electroplating of Bi_2Te_3 layers

microdevice fabricated by a MEMS-like electrochemical process.



. (a) SEM image of a completed p-/n-type couple ($\sim 20\ \mu\text{m}$ height); (b) SEM overview of entire completed microdevice. Reprinted with permission from ref. [128].

Electrodeposition of films

Take-home message

Low cost synthesis (low temperature, absence of vacuum, no advanced equipment)
High growth rate $1\mu\text{m/h}$ $50\mu\text{m/h}$
Thickness control by monitoring the consumed charge
Easy control by applied potential or current
Limited interdiffusion and chemical reaction
Scalability (large or small areas)
Conformal method

Selectivity

Polycrystalline state

Thickness = From tens of nm to hundreds of μm

Weak epitaxial relationship

chemical elements accessible depend mainly on the solvent

large range of chemical and electrochemical parameters (electroanalytical study)

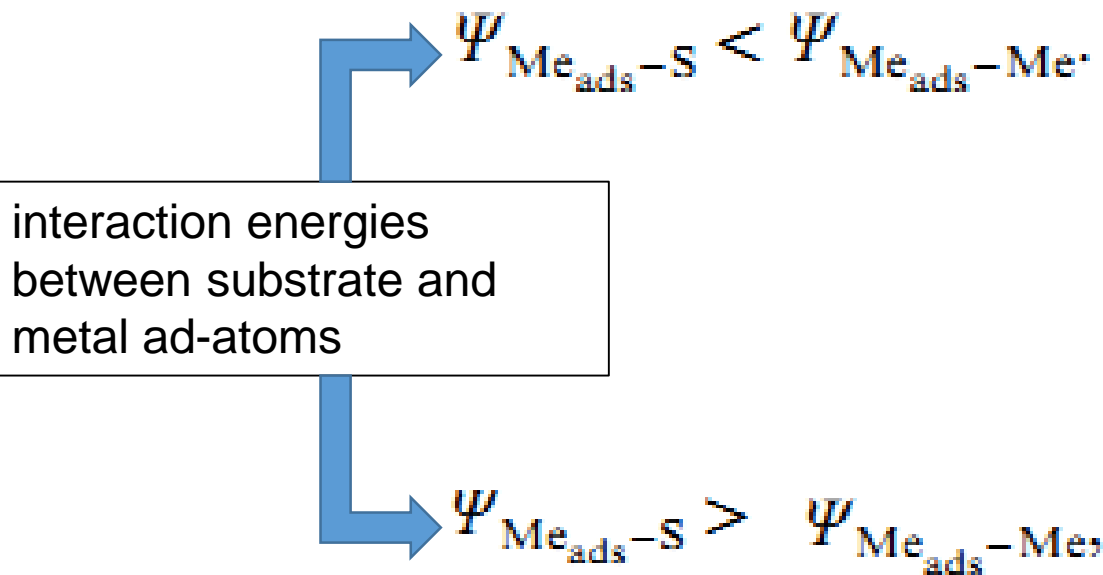
Need for electronic substrate

Contents

1. Electrosynthesis
 - a) Basics
 - b) Example : Bismuth Telluride
- 2. The synthesis of nanostructures by electrosynthesis**
 - a) Low dimensional films (2D)**
 - b) 1D nanostructures

The synthesis of nanostructures by electrosynthesis

Low dimensional films (2D)



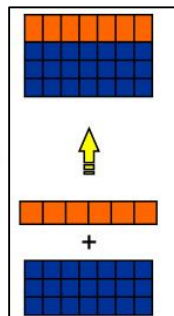
3D growth
independent of the
substrate/deposit lattice
matching (Volmer-Weber-type
growth)

Nucleation favored over any
crystallographic inhomogeneity
(dislocations, etc.) or surface
inhomogeneity (grain
boundaries, etc.).

Over Potential Deposition OPD

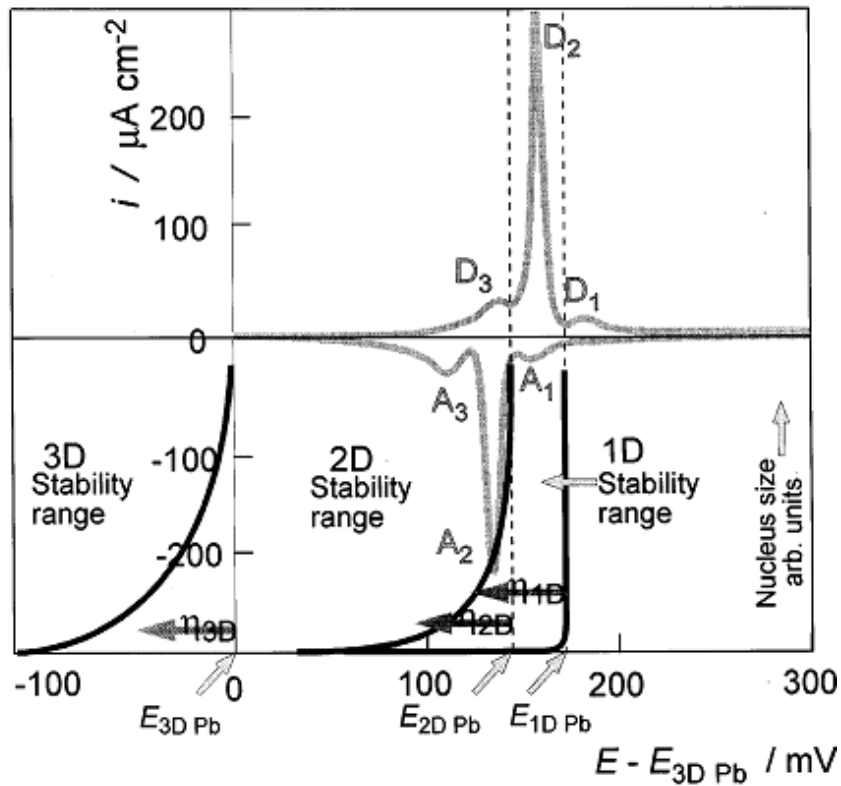
Possibility of low-dimensional
2D deposits...

on perfect atomic surface
Under Potential Deposition UPD



The synthesis of nanostructures by electrosynthesis

Low dimensional films (2D) : Under Potential Deposition



Example Ag(111)/Pb²⁺

Typical **An** Cathodic Adsorption peaks

Dn anodic desorption Peaks

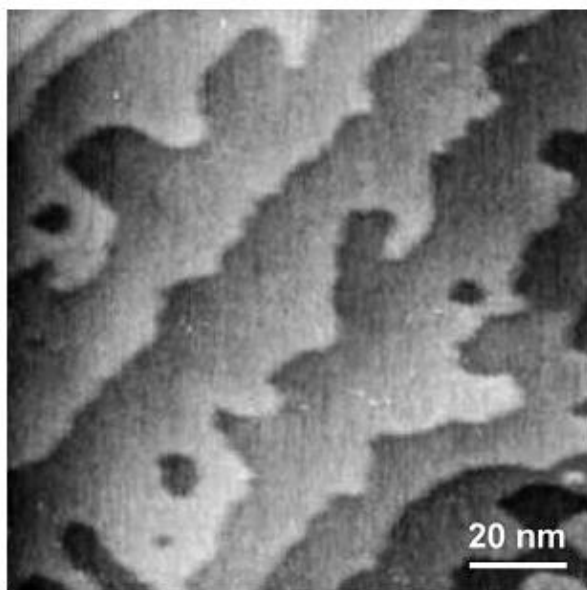
Black curve = sizes of the respective 1D, 2D and 3D nucleus as function of overpotential

Formation of more stable adsorption layer of Pb on single crystal of silver (111)

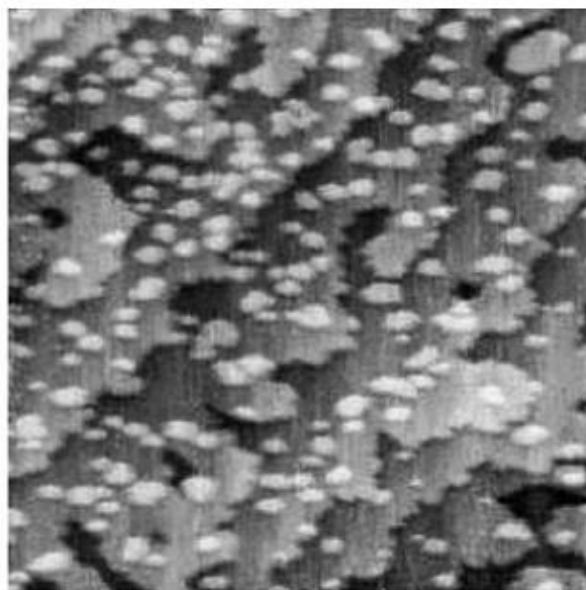
Growth at more positive potentials than bulk deposition (3D)

The synthesis of nanostructures by electrosynthesis

Low dimensional films (2D) : Under Potential Deposition



(a)



(b)

Example of Ag on a stepped Au (100) substrate

In Situ STM image

Formation of a Ag monolayer at UPD

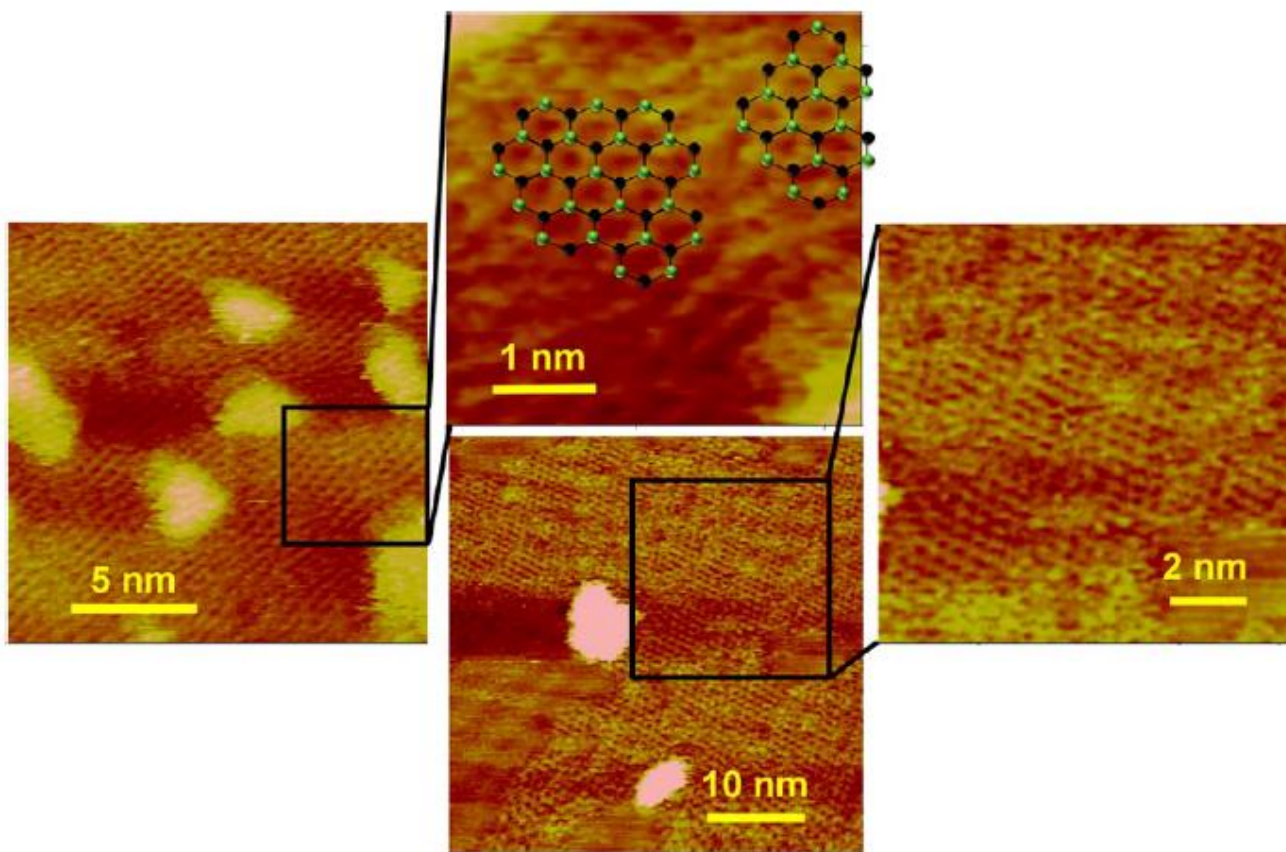
Figure 1.8. UPD of Ag on a stepped Au(100) substrate. Electrolyte: 5 mM Ag_2SO_4 + 0.1 M H_2SO_4 ($T = 298$ K). (a) *in situ* STM image of the substrate surface at underpotential $E - E_\infty = 400$ mV. (b) *in situ* STM image showing the formation of a condensed Ag monolayer at underpotential $E - E_\infty = 15$ mV.

The synthesis of nanostructures by electrosynthesis

Low dimensional films (2D) : Under Potential Deposition

Example of a 2D material = Germanene on Au (111)

- electrodeposition in an aqueous HGeO_3^- solution at pH 9.
- in situ EC-STM image
- distinct honeycomb structure
- Initial germanene nucleated at defects in the Au(111) herringbone (HB) reconstruction.



The synthesis of nanostructures by electrosynthesis

Low dimensional films (2D) :

ECALE electrochemical atomic layer epitaxy

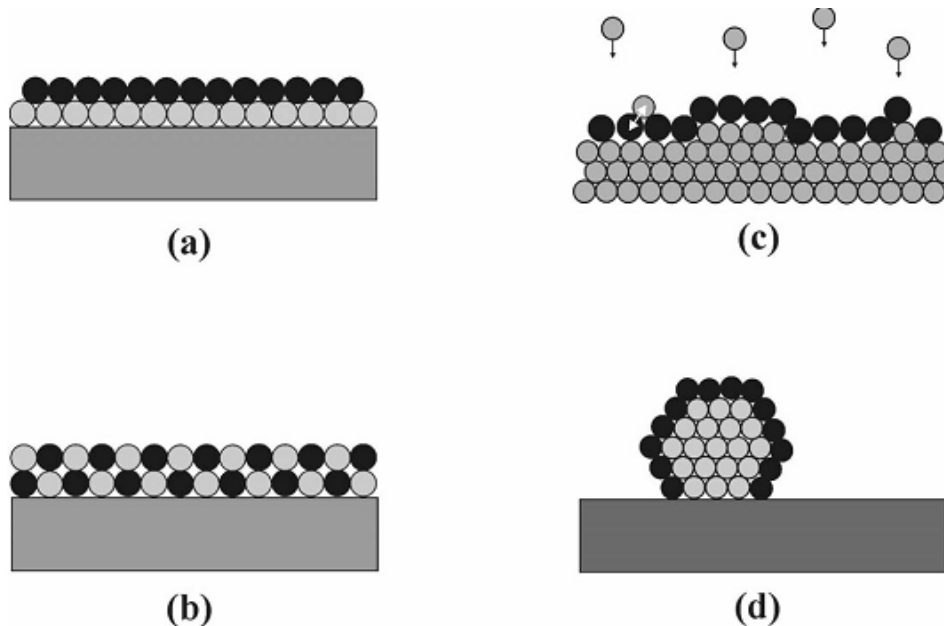


Figure 1.10. Possible applications of UPD in nanotechnology (a schematic representation). (a) deposition of superlattices and multilayers, (b) deposition of ultrathin alloy and compound films, (c) electrochemical surfactant mediated growth, (d) monolayer modification of nanoparticles.

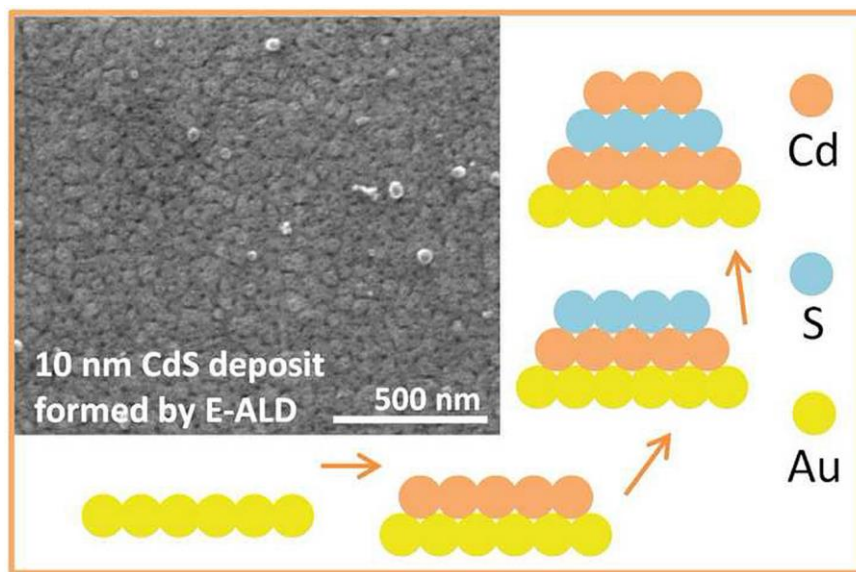
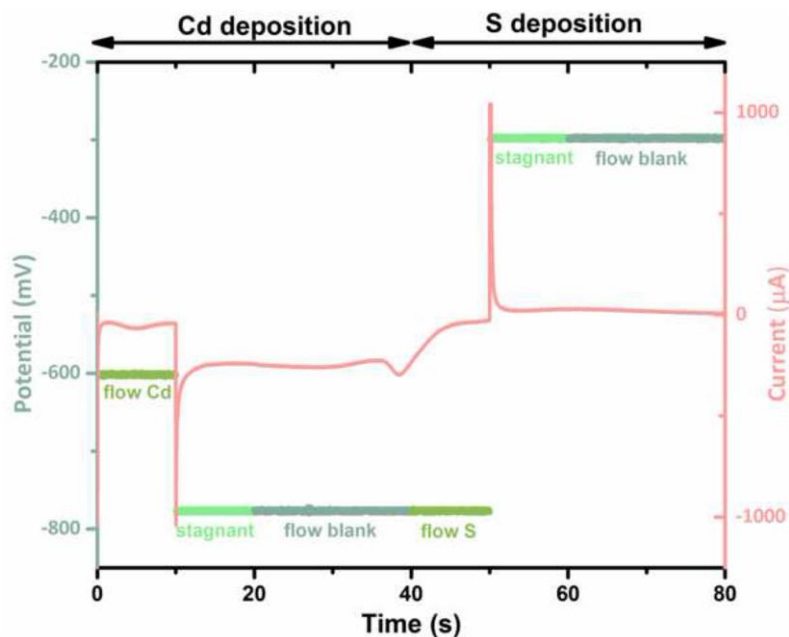
Possible applications of UPD in nanotechnology for duplex nanostructures

- a) superlattices and multilayers
- b) deposition of ultrathin alloy and compound films
- c) and d) Monolayer modification of nanoparticles or films

The synthesis of nanostructures by electrosynthesis

Low dimensional films (2D) : ECALE electrochemical atomic layer epitaxy

Formation of CdS thin film using electrochemical atomic layer deposition
by **sequential** underpotential deposition



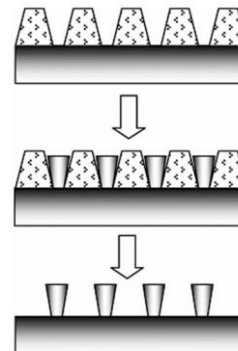
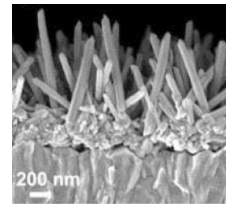
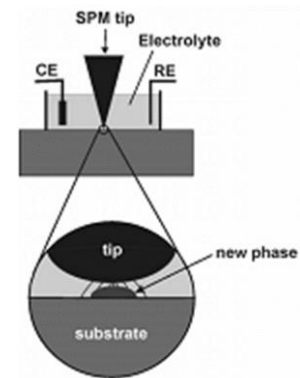
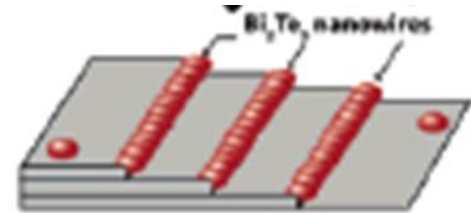
Contents

1. Electrosynthesis
 - a) Basics
 - b) Example : Bismuth Telluride
2. The synthesis of nanostructures by electrosynthesis
 - a) Low dimensional films (2D)
 - b) 1D nanostructures**

Electrodeposition of nanowires

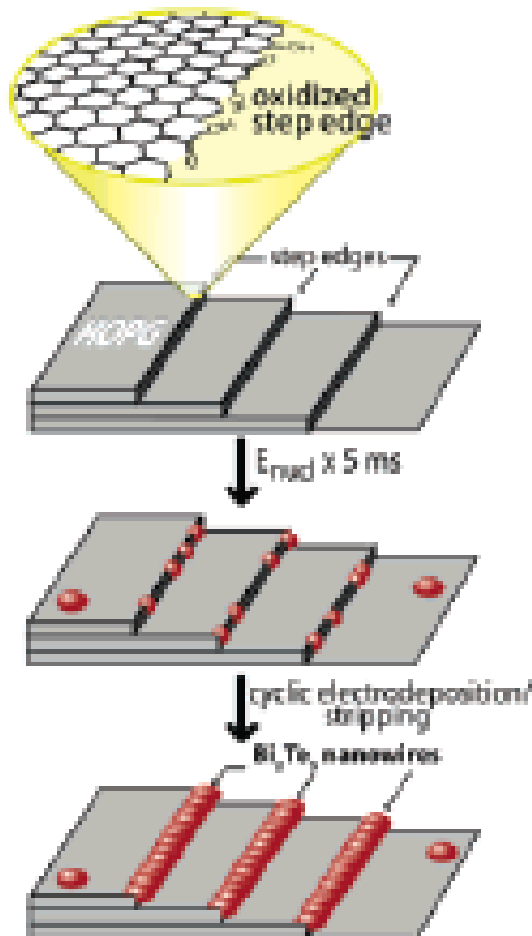
Synthesis strategies

- Electrochemical Step Edge Decoration
- Assisted by Scanning Probe Microscope
- Self-assembly synthesis
- Template Synthesis



Electrodeposition of nanowires

Electrochemical Step Edge Decoration



Substrate = Highly Oriented Pyrolytic Graphite

Electrodeposition preferred along the edges of the substrate

Presence of crystalline defects along steps with high charge transfer kinetics

Electrodeposition of nanowires

Electrochemical Step Edge Decoration

Example of Copper Nanowires

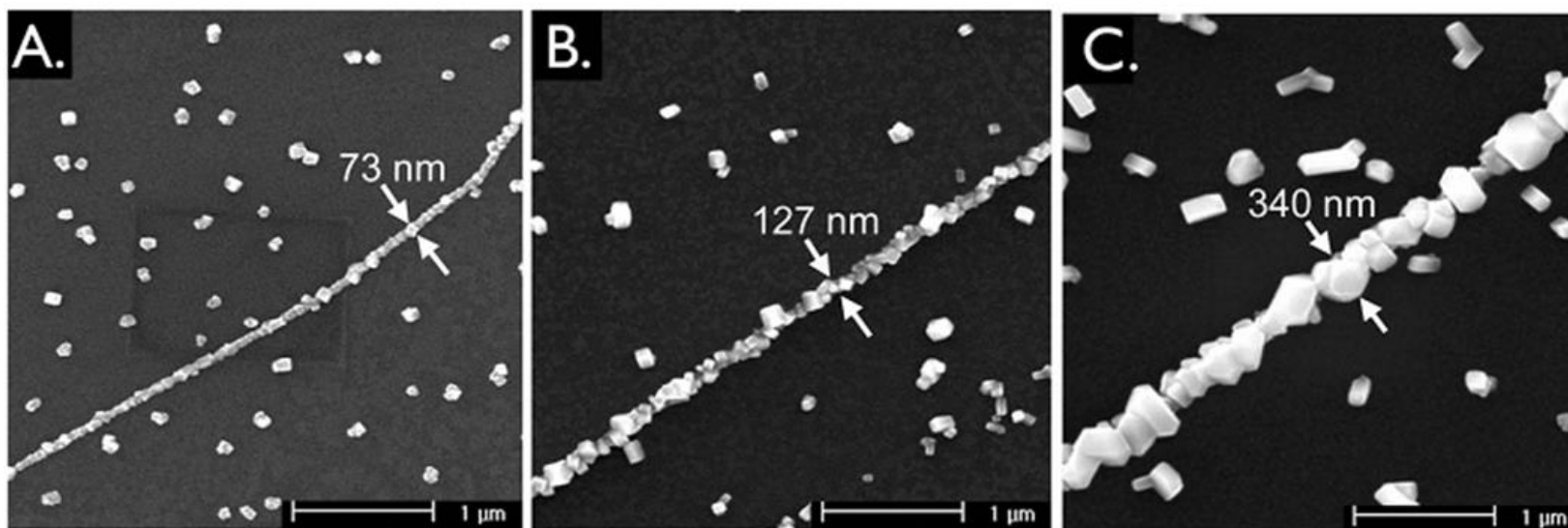
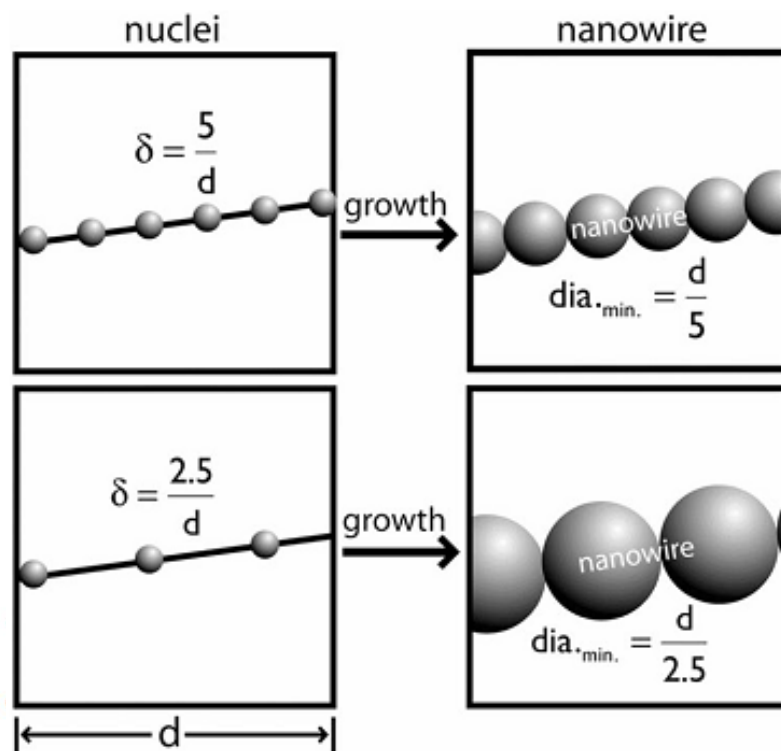


Figure 9.5. Scanning electron micrographs of copper nanowires. These nanowires were electrodeposited from an 2.0 mM $\text{CuSO}_4 \cdot 5\text{H}_2\text{O}$, 0.1 M Na_2SO_4 using $E_{\text{nucl}} = -800 \text{ mV}_{\text{SCE}}$ and $E_{\text{grow}} = -5 \text{ mV}_{\text{SCE}}$. The growth times employed in each experiment were: A, 120 s; B, 600 s; C, 2700 s.

Electrodeposition of nanowires

Electrochemical Step Edge Decoration

Reciprocal relationship between the nucleation density and minimum nanowire diameter

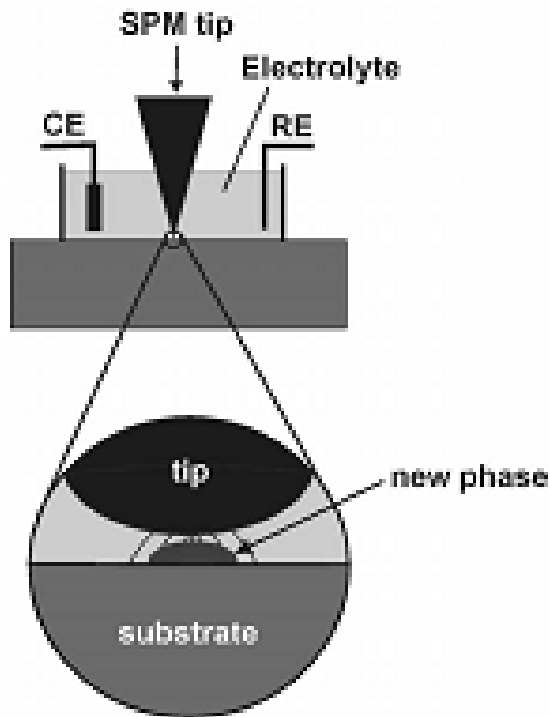


Material	ESED Method	Wire diameter (nm)	Functional properties evaluated
Mo	E/C ^(a)	1000–15	electrical
MoO ₂	direct	1250–20	none
MnO ₂	direct	150–40	none
Pd	direct	500–50	electrical, hydrogen sensing
Ag	direct	1000–200	electrical, ammonia sensing
Pt, Cu	direct	750–60	electrical
Ag _x O	direct	1100–700	electrical, ammonia sensing
Au	direct + EO ^(b)	300–50	none
Sb	direct + EO	300–30	none
Bi ₂ Te ₃	cyclic ED/S ^(c) + EO	300–30	electrical, thermoelectric power generation
CdSe	cyclic ED/S	300–30	photoluminescence
CdS	E/C	116–550	photoluminescence, photoconductivity
MoS ₂	E/C	800–50 (w) × 3–100 (h)	optical absorbance
SiO ₂	CVD ^(d)	80 (w) × 20–40 (h)	none

... ..

Electrodeposition of nanowires

SPM-assisted nanostructuring



Localized electrodeposition between the tip and the substrate

$$R_{\text{electrolyte}}/R_{\text{polarisation}} \gg 1$$

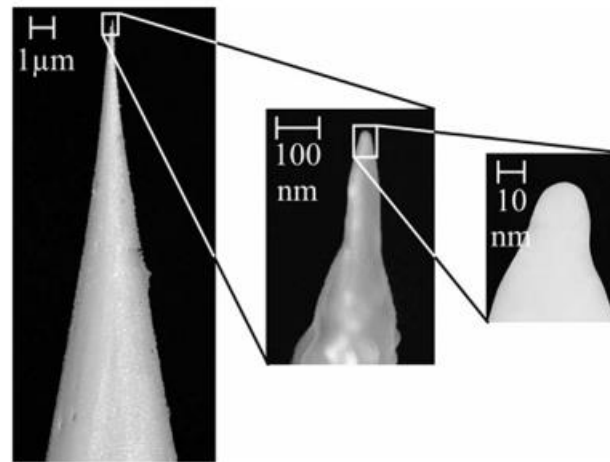


Figure 6.9. Scanning and transmission electron images of Au STM tips, as prepared with the combined field emission/sputtering technique. The diameter of the STM tip apex is approximately 20 nm.

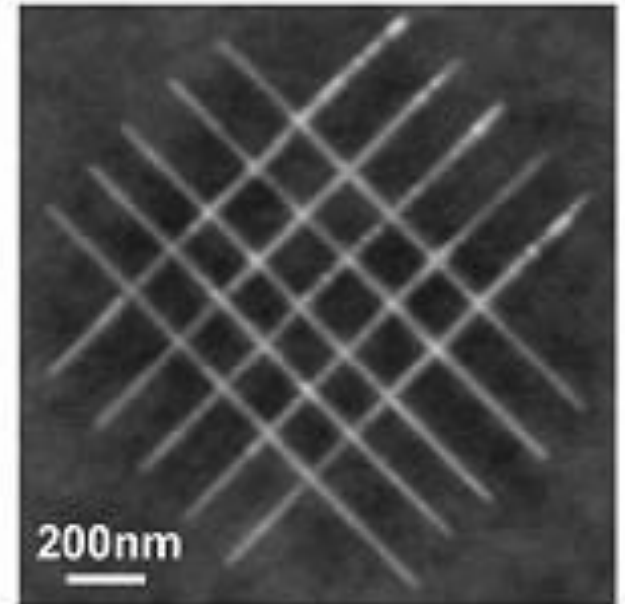
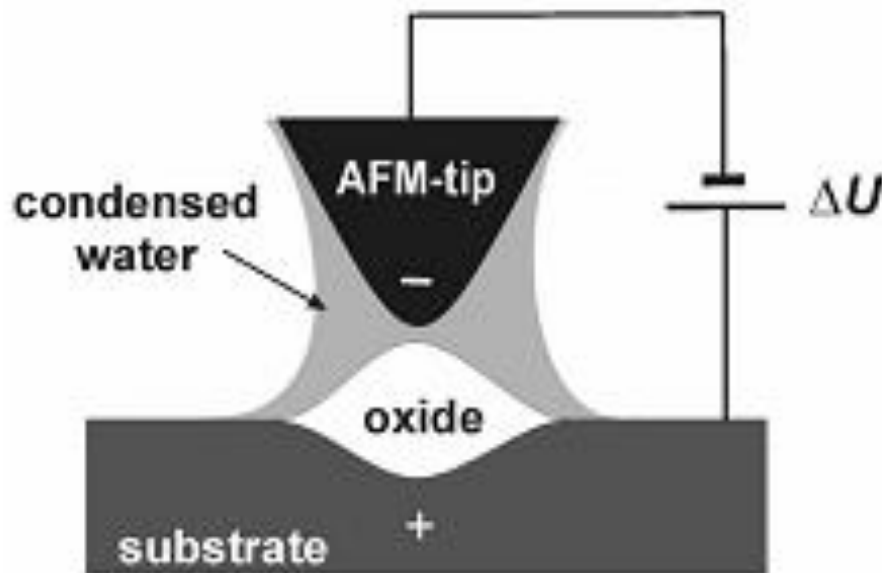
Electrodeposition of nanowires

SPM-assisted nanostructuring

Localized anodic oxidation induced by the AFM tip

SiO₂ pattern fabricated by I₀ tip-induced oxidation of p-Si(111) substrate

Relative humidity 3%



Electrodeposition of nanowires

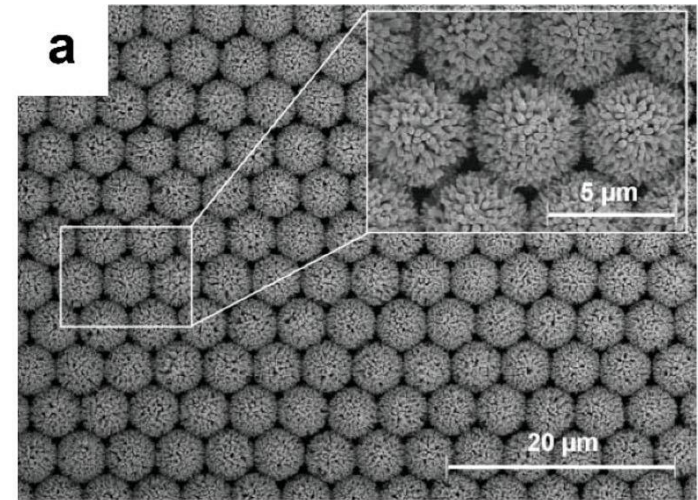
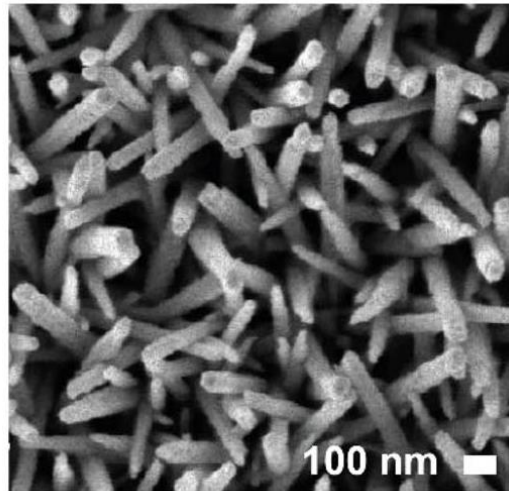
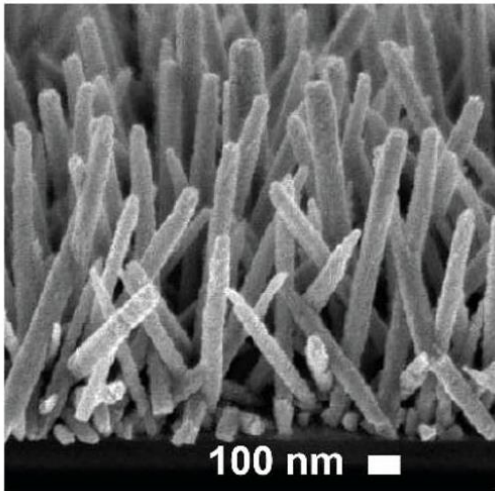
Self-assembly synthesis : in aqueous medium

Template less synthesis of single crystalline ZnO nanowires

single crystalline ZnO nanowires



Source of hydroxide ions : Molecular oxygen, Nitrate ions, Hydrogen peroxide



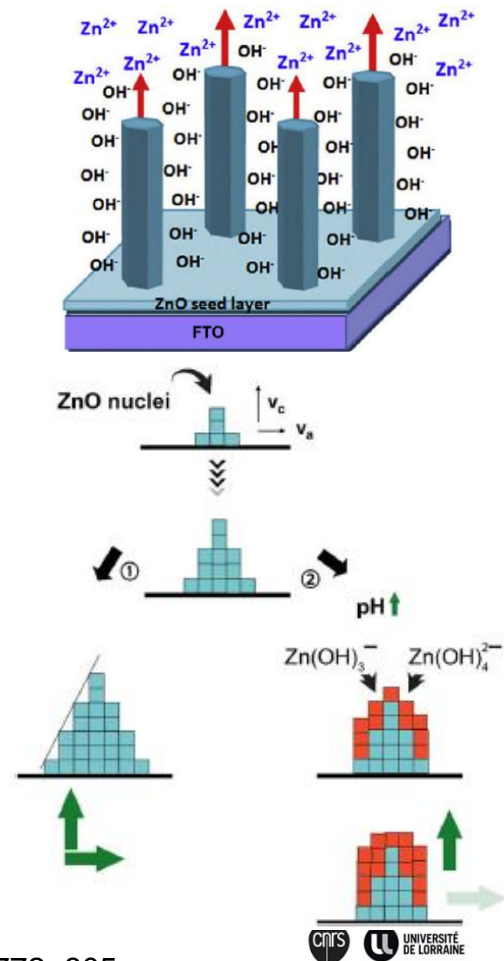
FE-SEM micrographs of ZnO nanowires deposited on copper and on polystyren spheres (bioinspired sea urchins)

Electrodeposition of nanowires

Self-assembly synthesis : in aqueous medium

Template less synthesis of single crystalline ZnO nanowires rapid growth along the longitudinal axis :

- Diffusion rate of Zn(II) species is significantly less than the rate formation of the hydroxide ions
- Adsorption of the negatively charged Zn(II) species as well as the hydroxide ions on the top Zn-terminated (0001) polar plane of the hexagonal ZnO crystals,



Electrodeposition of nanowires

Self-assembly synthesis : in ionic liquid

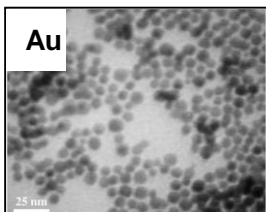


Materials containing only ions

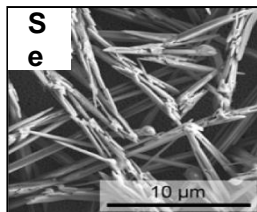
$$T_{\text{melt}} < 100^{\circ}\text{C}$$

Some are liquid at Room Temperature : RTILs

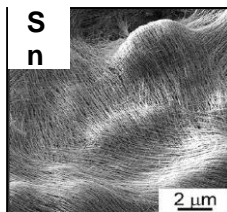
- + Low vapor pressure ➡ Low inflammability, low volatility
- + Wide electrochemical window ➡ Electrodeposition of reactive elements
- + High thermal stability ➡ High cristallinity of materials
- + Capping agents ➡ **Template-free nanostructures synthesis**



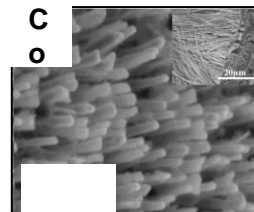
Absalan et al.,
Coll. Surf. A (2015)



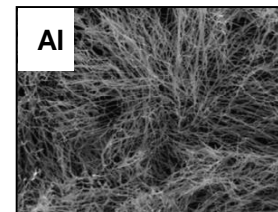
Steichen et al.,
Electrochem. Comm.
(2011)



Al-Salman et al.,
Chem. Mater (2015)



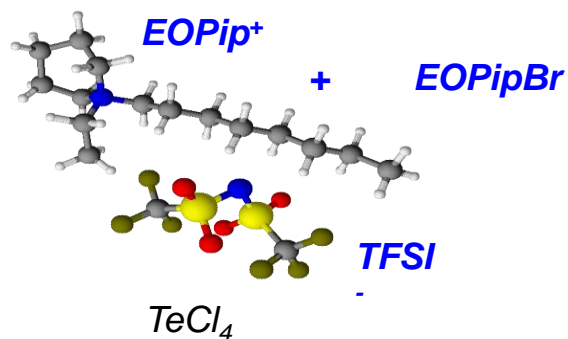
Hsieh et al.,
Electrochim Acta (2014)



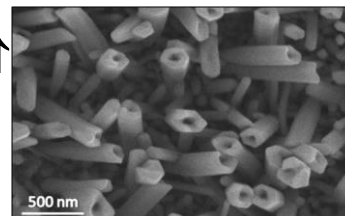
Su et al.,
Electrochem Comm (2013)

Electrodeposition of nanowires

Self-assembly synthesis : in ionic liquid

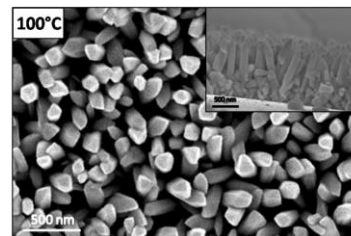


overpotential \uparrow



Hollow nanostructures

$AR \approx 10$

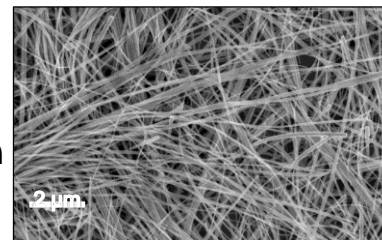


Nanorods

Aspect Ratio ≈ 13



Te^{IV} speciation
[Br^-]



Hair-like
nanowires

$L = 70 \pm 10 \mu m$
 $\varnothing = 50 \pm 20 nm$

$AR \approx 1800$

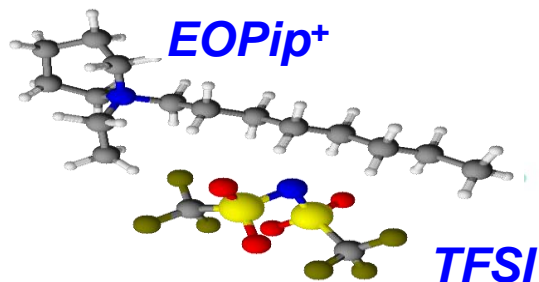
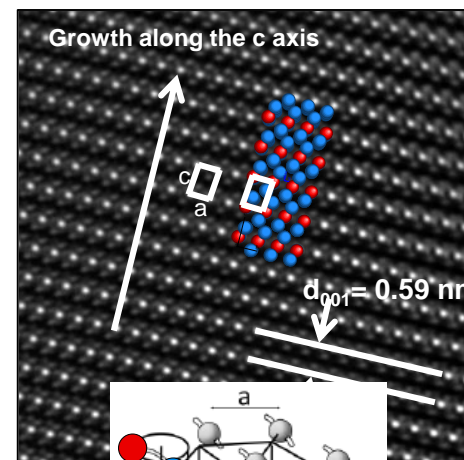
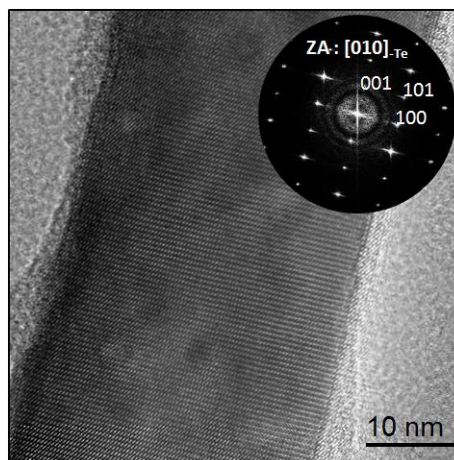
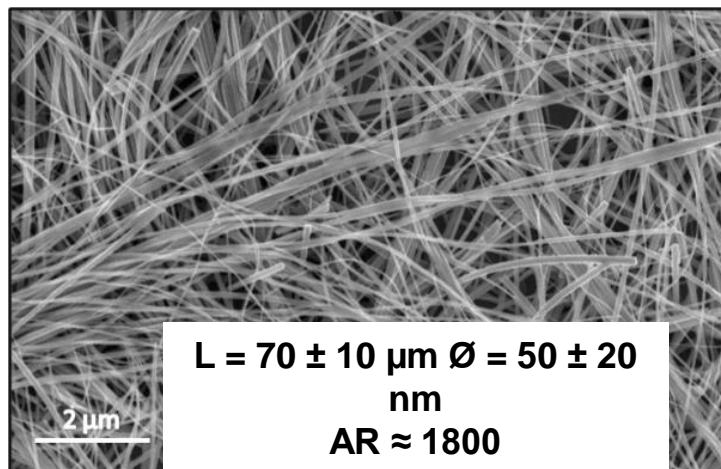
Electrodeposition of nanowires

Self-assembly synthesis : in ionic liquid

$T = 100^{\circ}\text{C}$
 $[\text{Te}^{\text{IV}}] = 5 \text{ mM}$, E_p
 $\% \text{ Br} = 0,2 \%$

0.2 % EOPipBr

HRTEM analysis



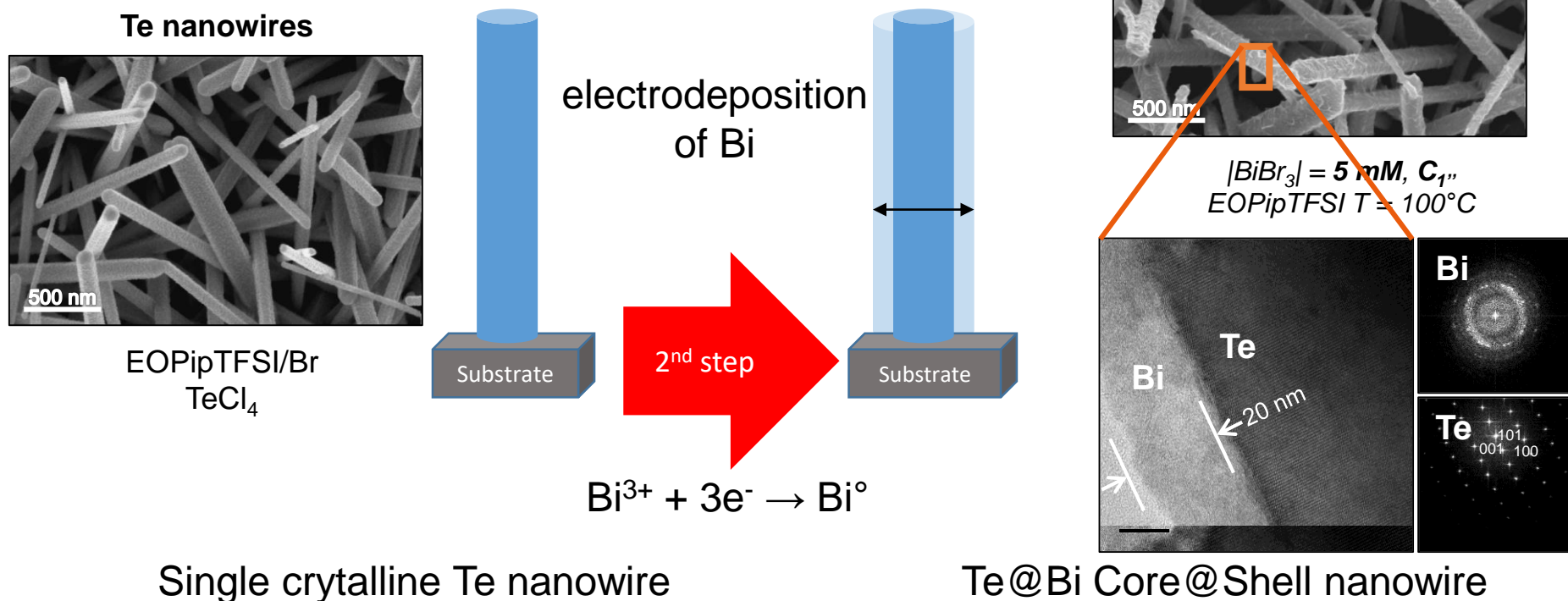
Bis(trifluorométhylsulfonyl)imidure

Specific mass transport (viscosity)
 Anisotropic structure of Te

Thiebaud et al., *Electrochimica Acta* 197 (2016)

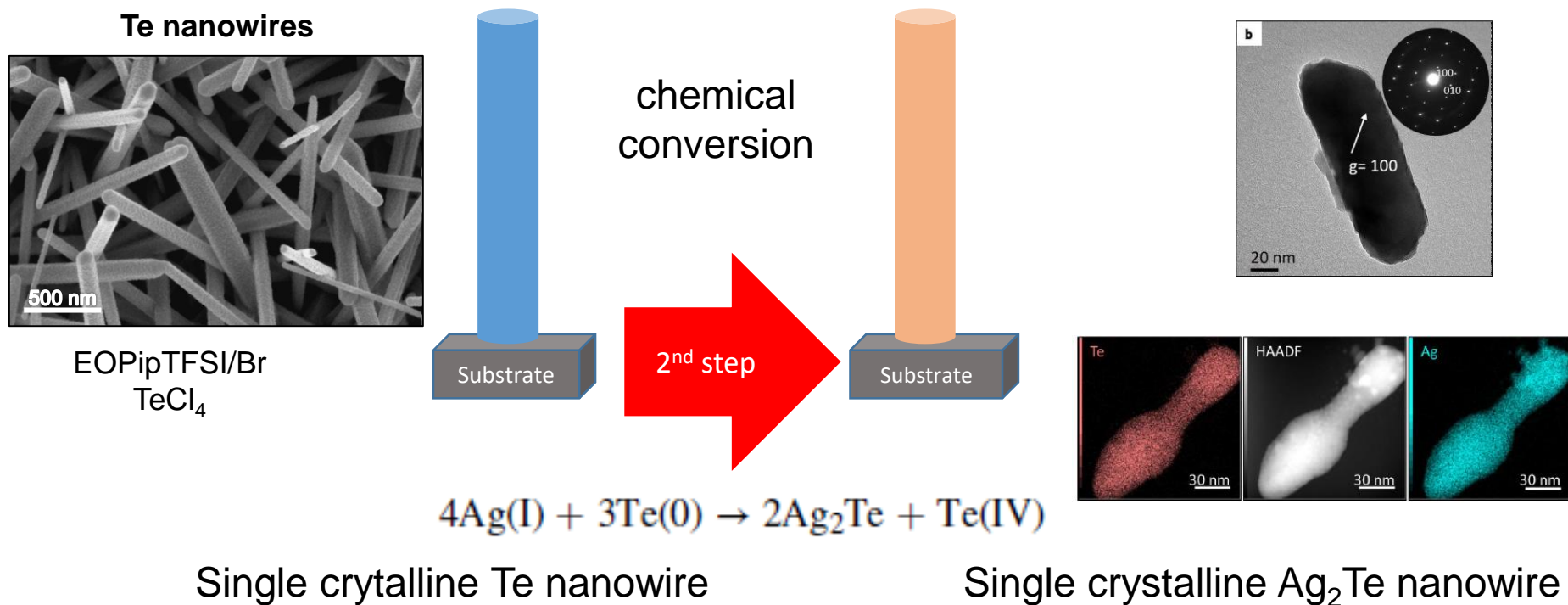
Electrodeposition of nanowires

Self-assembly synthesis :
2 step synthesis of core@shell NWs



Electrodeposition of nanowires

Self-assembly synthesis :
2 step synthesis of binary compounds



Electrodeposition of nanowires

The template synthesis

- bottom-up approach

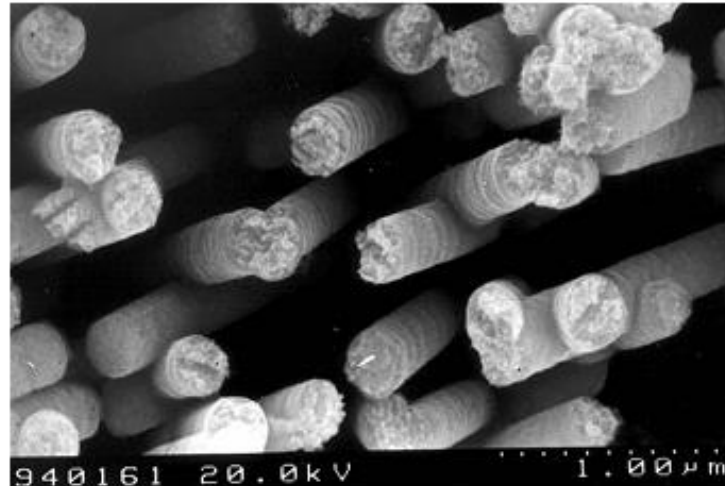
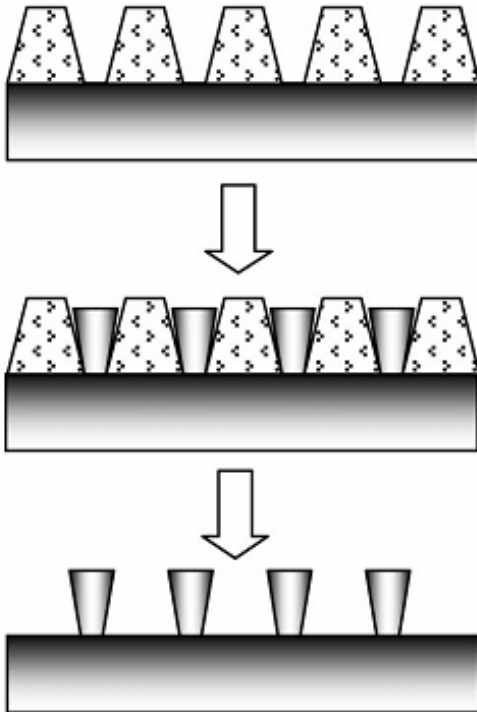
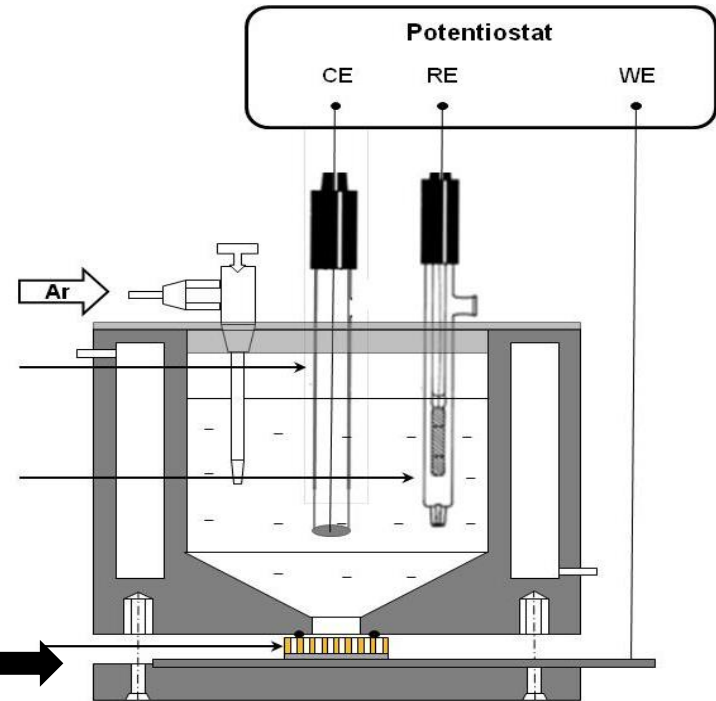
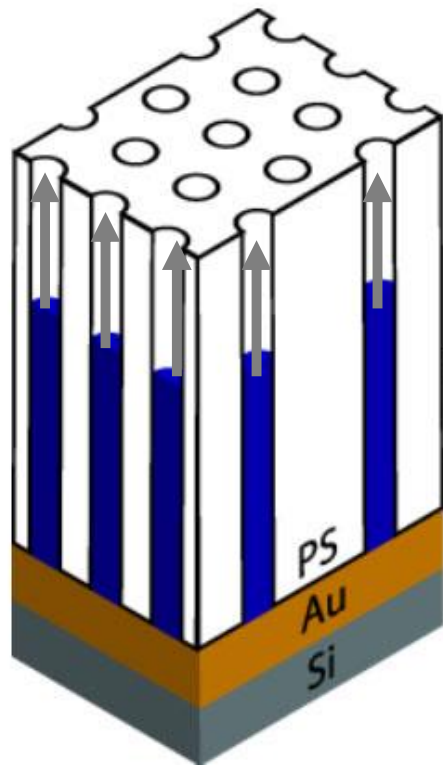


Figure 3.3. Single crystalline gold nanowires in a poly-carbonate track-etched (PCTE) membrane template after dissolution of the template [13].

Electrodeposition of nanowires

The template synthesis

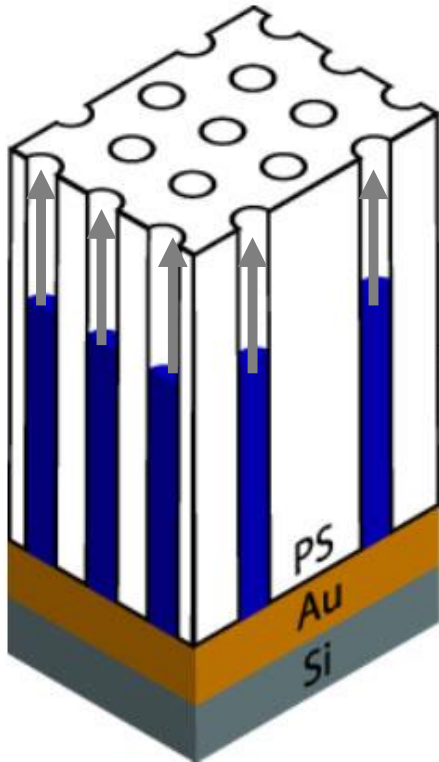


Exposed area : 0,785 cm²

- ✓ Membrane = array of ultra-microelectrodes
- ✓ Filling = Cathodic reduction $M^{n+} + ne^- \rightarrow M^0$

Electrodeposition of nanowires

The template synthesis : 1/the membrane



❖ Dimensions of nanowires directly linked to those of membrane pores

- Nanowires 1D nanostructures
- Length : 1 - 100 μ m
- Diameter : 10 – 200 nm
- High diameter/length ratio

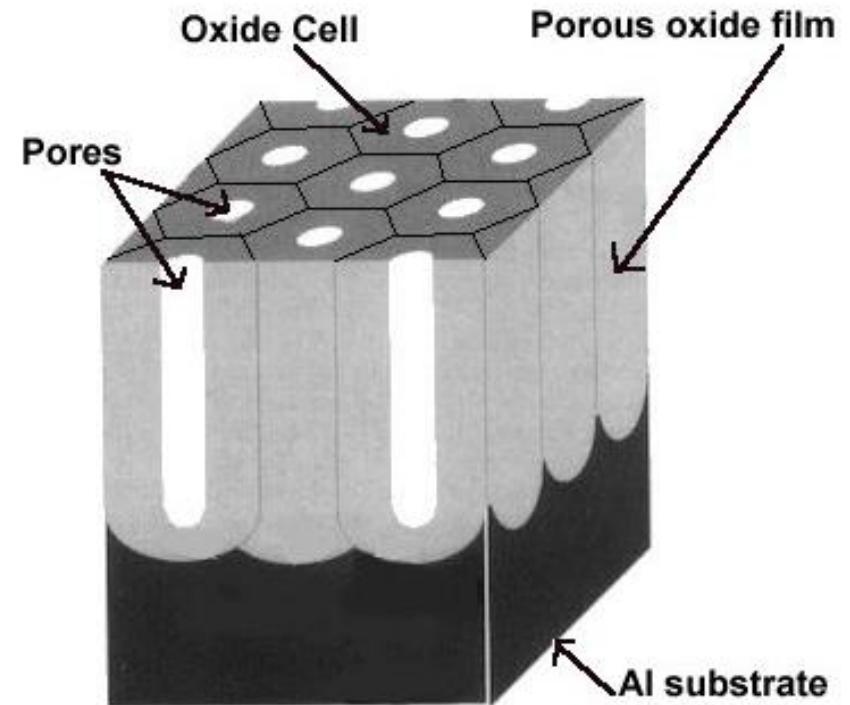
❖ Physical properties of the template

- insulating (electronic and thermal conductivity)
- mechanical resistance
- temperature resistance

Electrodeposition of nanowires

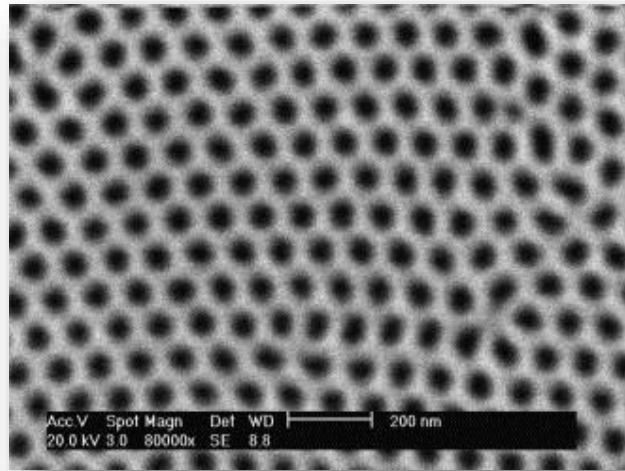
The template synthesis : 1/ the membrane porous AAO anodized aluminium oxide films

- ✓ **Anodization of high purity aluminium** in mineral acid
- ✓ uniform spatial distribution of vertical pores in honeycomb cells (hexagonal symmetry)
- ✓ Presence of insulating, dense oxide layer (called **barrier layer**) separating the Al substrate and the porous oxide film
 - *thinning the barrier layer**
- ✓ **Geometric parameters** (pores size, radius, density) linked to anodization parameters (electrolyte, anodizing voltage)

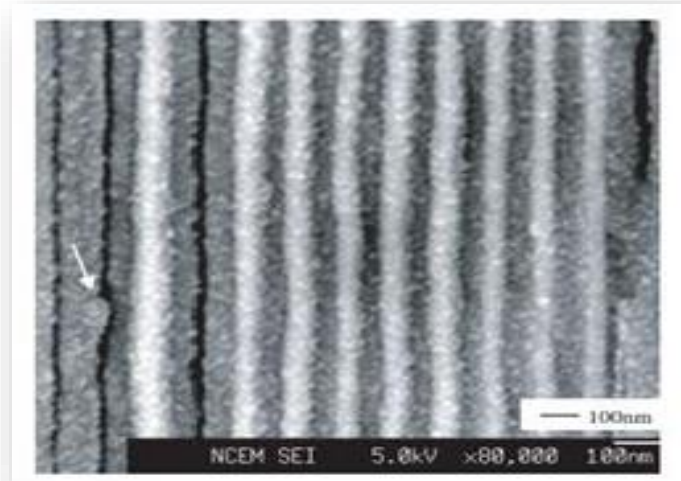


Electrodeposition of nanowires

Template synthesis : : 1/ the membrane
porous AAO anodized aluminium oxide films



Top view



Cross section

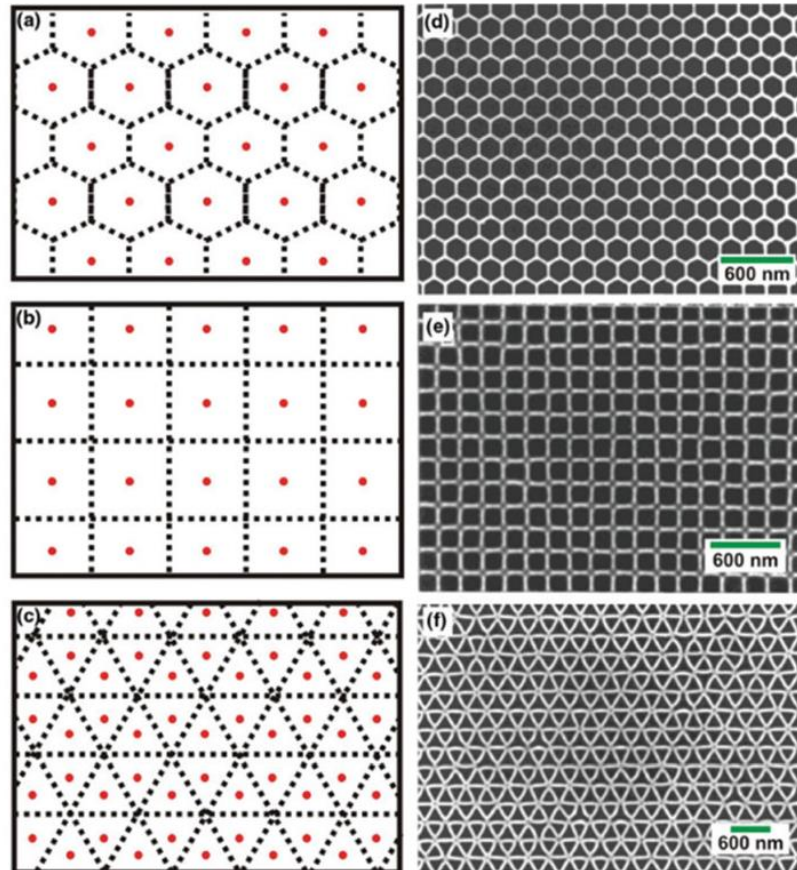
- ✓ Porous structure ~ a honeycomb array
- ✓ High pore density $> 10^9$ pores/cm²
- ✓ Range of thickness = 10 – 100 μ m
- ✓ Commercial products (filtration) = interconnection between nanopores

The most popular template in the literature (possibility of annealing)

Electrodeposition of nanowires

Template synthesis : : 1/ the membrane
porous AAO anodized aluminium oxide films

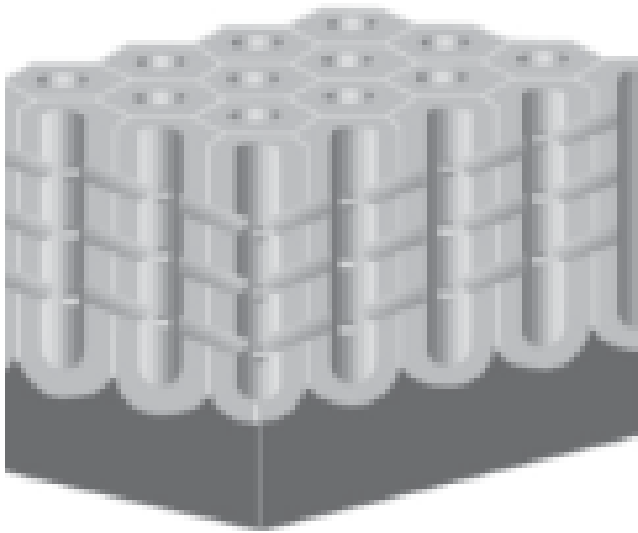
Cell representations and SEM images of
prepatterned AAO in three exemplary geometries.



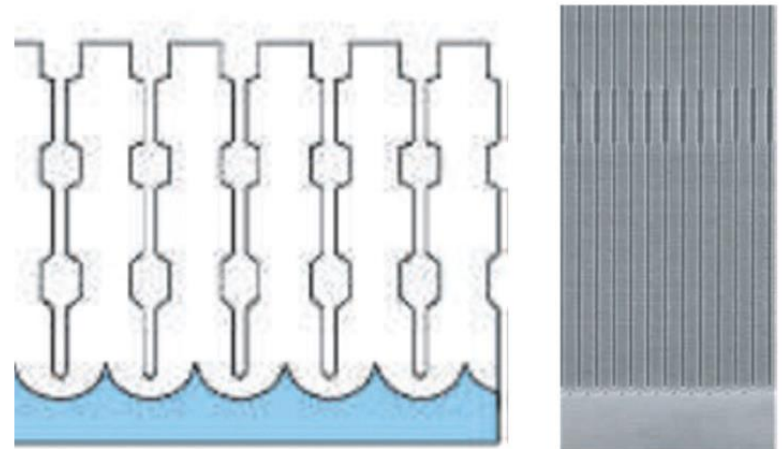
Electrodeposition of nanowires

Template synthesis : : 1/ the membrane
porous AAO anodized aluminium oxide films

3D anodic porous alumina template



Schematic and SEM image of a
diameter modulated AAO
membrane.



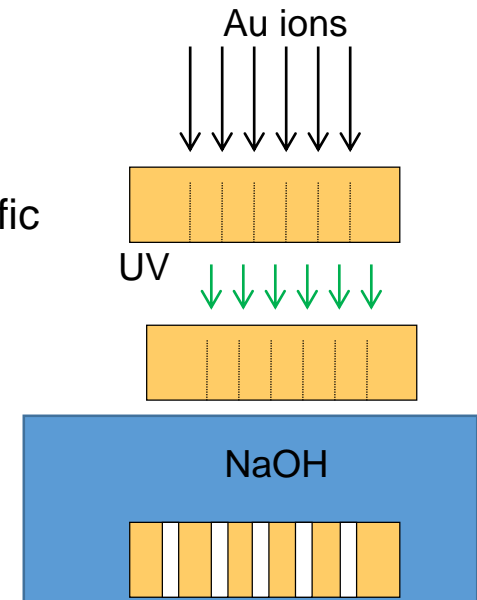
Caballero-Calero, O.; Martín-González, M.
Scripta Materialia 2016, 111, 54-57.

Electrodeposition of nanowires

**Template synthesis : : 1/ the membrane
ion-track etched polymeric membranes ITEP**

Synthesis of ITEP membranes

1. **Irradiation** of polymeric foils with single Au ions of 11.4 MeV/u specific kinetic energy at heavy ion linear accelerator
2. **Exposition to UV** light for 1 h
3. **Etching of the nanopores** in aqueous NaOH



Polymers

polycarbonate, polyethylene terephthalate, polyimide

Electrodeposition of nanowires

**Template synthesis : : 1/ the membrane
ion-track etched polymeric membranes ITEP**

Typical dimensions

Low pore density: $10^8 - 10^9$ pores/cm²,

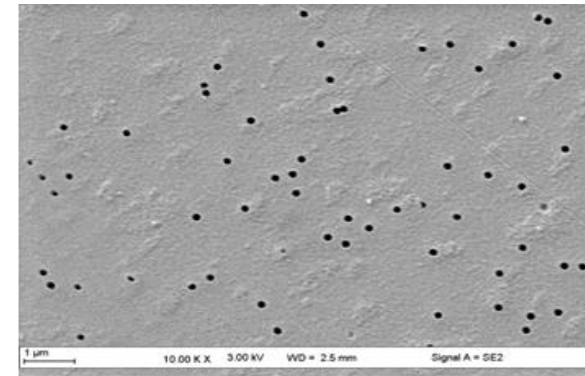
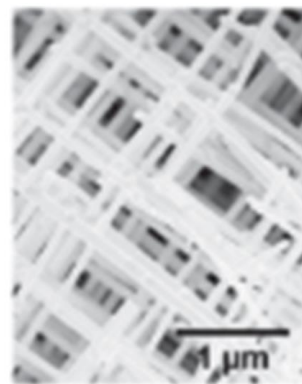
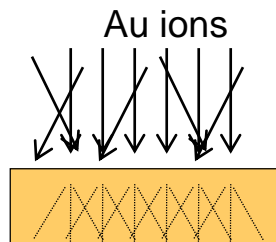
thickness 5 – 50 μm

maximum aspect ratio 1 / 1000

Potential defects: twin pore

Tunable dimensions by chemical post etching

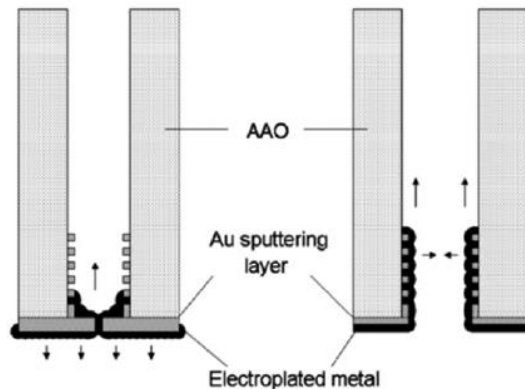
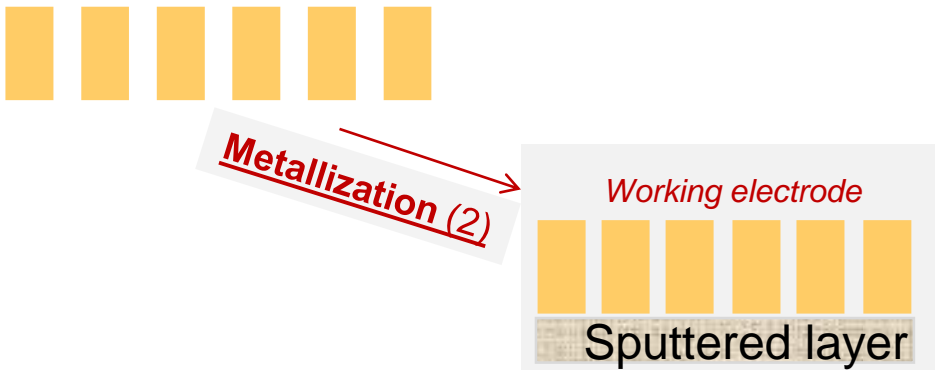
3D nanowire network prepared
in ion-track etched membranes



Top view
Pore density $3 \times 10^9 \text{ cm}^{-2}$

Electrodeposition of nanowires

Template synthesis : 2/ the metallization step



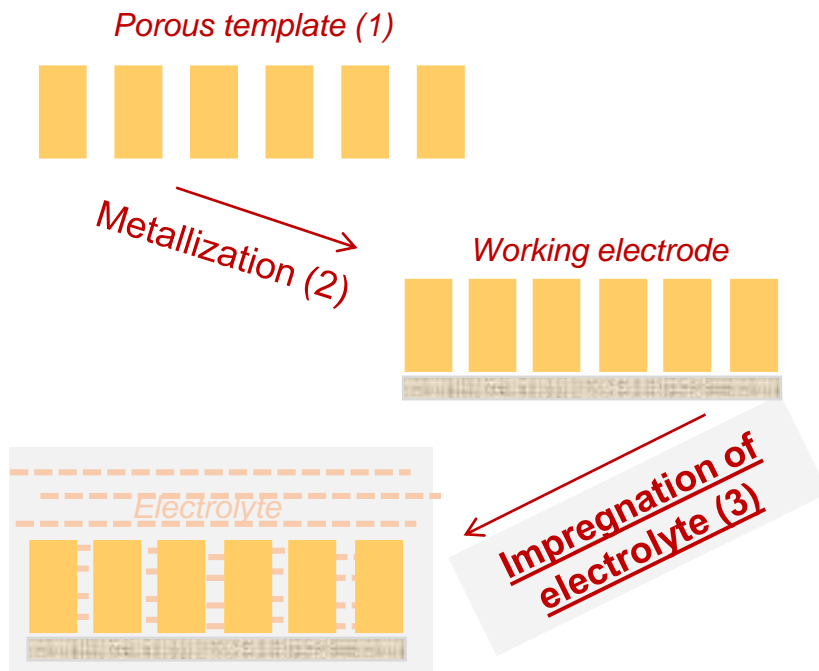
Adjustment of the sputtering parameters

- homogenous surface
- high electrochemical reactivity at the bottom of **each** pore
- High quality of the electrical contact for lowest internal resistances
- Adhesion
- Influence of metal layer on the electrochemical behavior
- Sealing of pores : thickness > diameter
- Problem of coating along the pore walls

Fig. 6 (A) Influence of the contact sputtering process of a blocked and unblocked membrane onto the seed formation and the following electro-deposition of nanomaterial. (B) SEM images of the resulting CoPt nanotubes and nanowires. Reproduced with permission from J. Fu, S. Cherevko and C.-H. Chung, *Electrochem. Commun.*, 2008, **10**, 514.⁵⁷

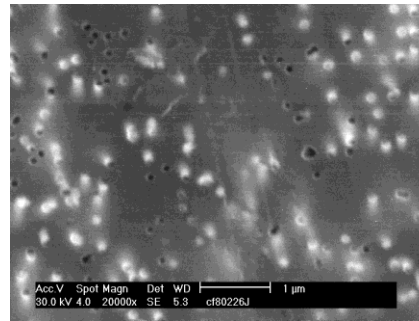
Electrodeposition of nanowires

Template synthesis : 3/ the impregnation step

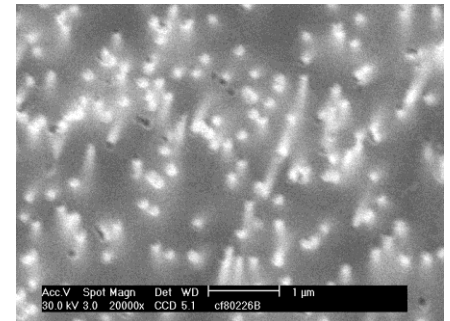


Optimal filling by impregnation whatever the pore sizes = example of polycarbonate membranes

■ Pretreatment: sonication of the template in the electrolyte for 2 min



sonication: 0 minute

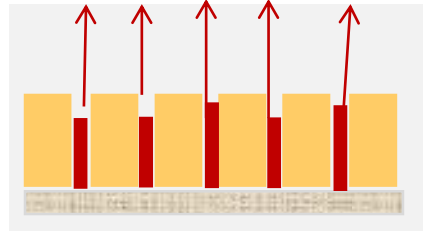


sonication: 2 minutes

■ Wetting reagent : addition of DMSO in the electrolyte (50% v/v)

Electrodeposition of nanowires

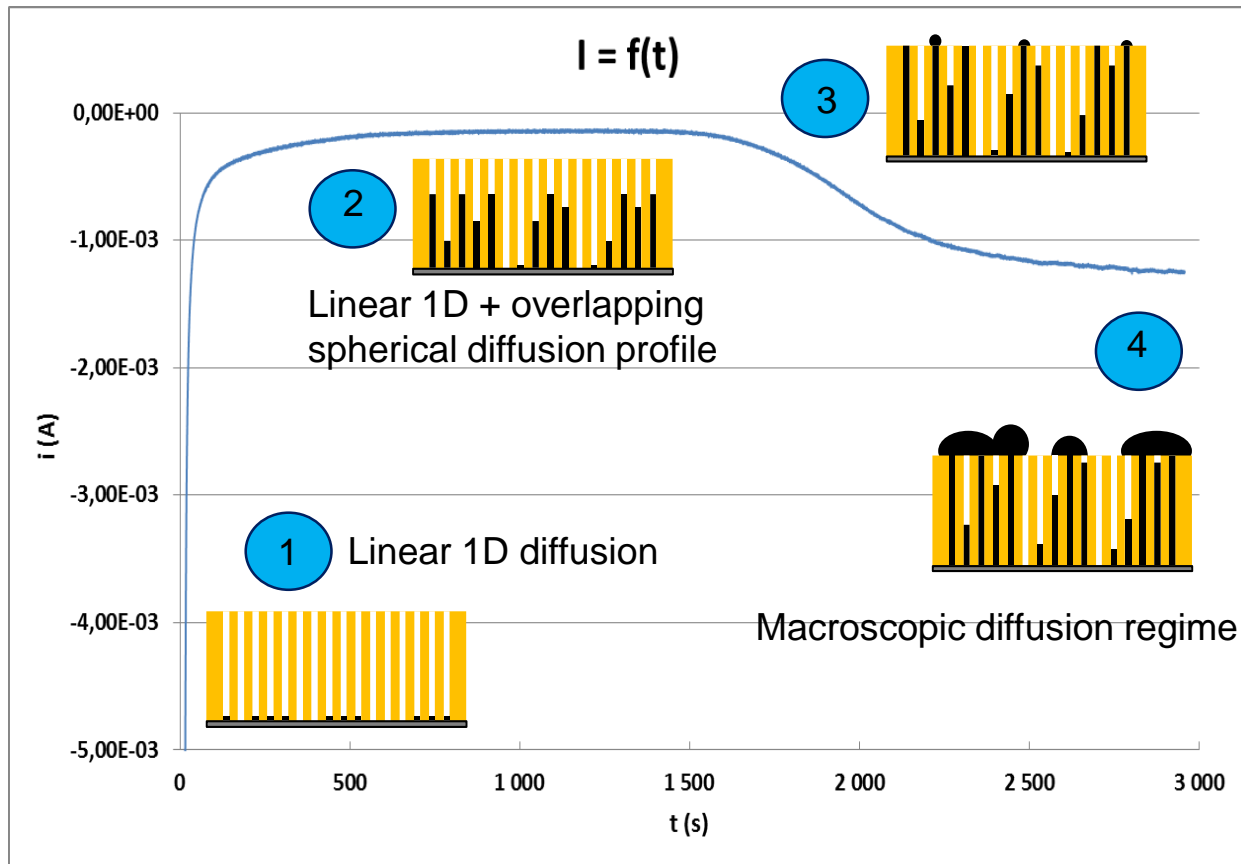
Template synthesis : 4/ the electrocrystallization step



- homogenous filling between the pores → Growth rate
- homogeneous chemical composition along the NWs → Diffusion of ionic species
- growth process → Crystallinity
- No homogenous rate in each pore = filling ratio below 100 %
 - Improvement by lower growth rate (diffusion rate)
 - Improvement by pulse electrodeposition

Electrodeposition of nanowires

Template synthesis : 5/ Growth (chronoamperometric curve)

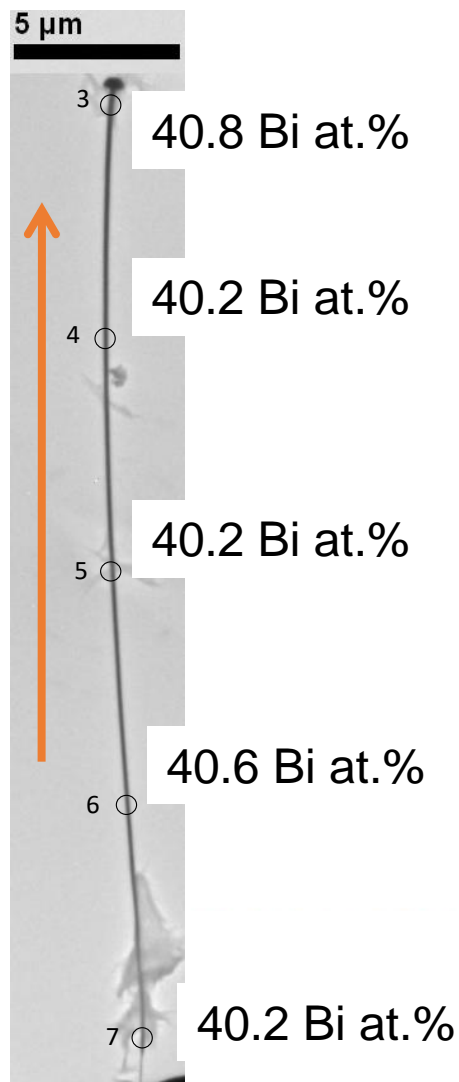


1. Nucleation
2. Growth
3. Filling
4. Coalescence and formation of an upper layer

Specific mass transport regimes

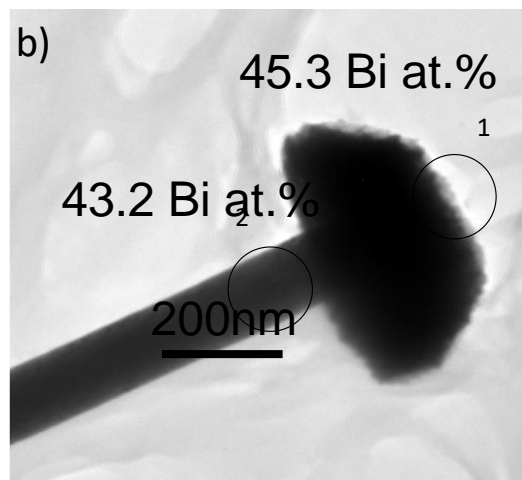
Electrodeposition of nanowires

Template synthesis : 5/ Growth



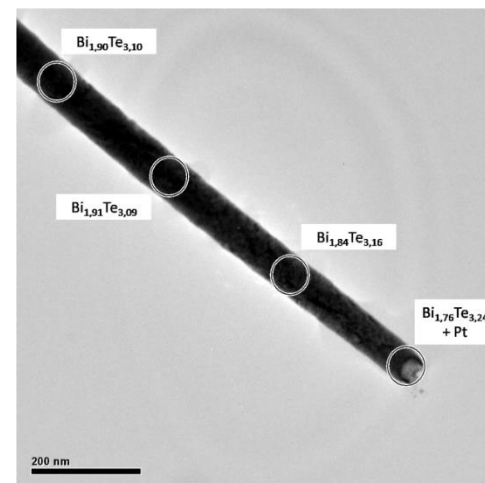
- Example : electrodeposition of Bi_2Te_3 nanowires
- No deviation of the chemical composition along the nanowires = steady state diffusion regime

Zoom : cap



- ✓ Enrichment of Bi
- ✓ Form texture
- ✓ Change of cation diffusion

Zoom : bottom



- ✓ Enrichment of Te
- ✓ Polyphased state
- ✓ Bi_2Te_3 Te°
- ✓ Poly-crystalline

Electrodeposition of nanowires

Template synthesis : electrocrystallization

The critical dimension N for a 2D-like nucleus
$$N_c = \frac{bS\varepsilon^2}{(Ze\eta)^2}$$

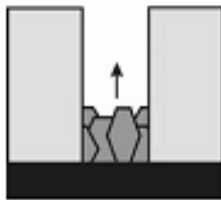
S = surface area occupied by an atom on the surface of a nucleus

ε = surface energy

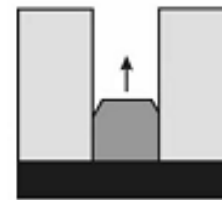
Z = effective electron number

η = overpotential

B = constant



new grains will grow if the size of an initial cluster exceeds the critical dimension N

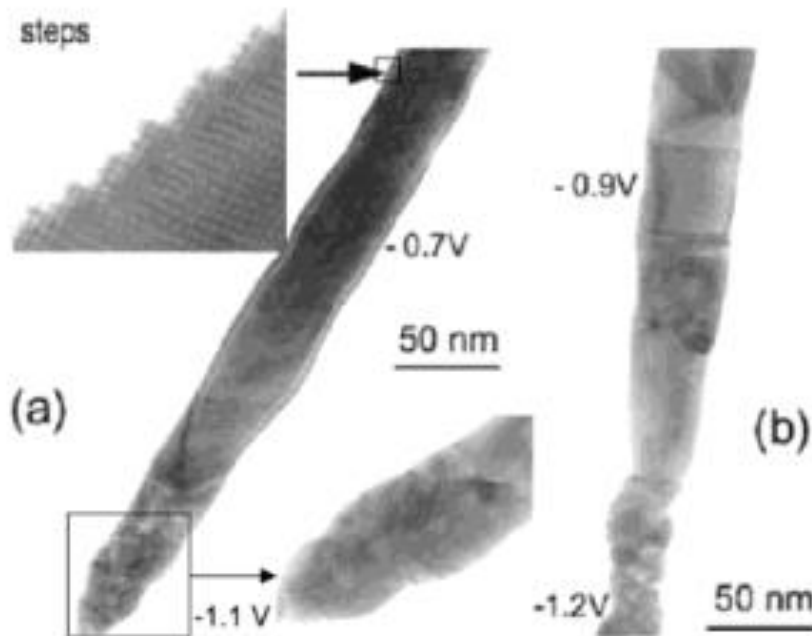


The larger the N is, the more favorable it is for a single crystal to grow from a previously nucleated seed grain.

Electrodeposition of nanowires

Template synthesis : electrocrystallization

$$N_c = \frac{bS\varepsilon^2}{(Ze\eta)^2}$$



Influence of the overpotential η

TEM images of Au nanowires with varying potentials

Electrodeposition of nanowires

Template synthesis : electrocrystallization

$$N_c = \frac{bS\varepsilon^2}{(Ze\eta)^2}$$

Influence of the effective electron number Z

TEM images

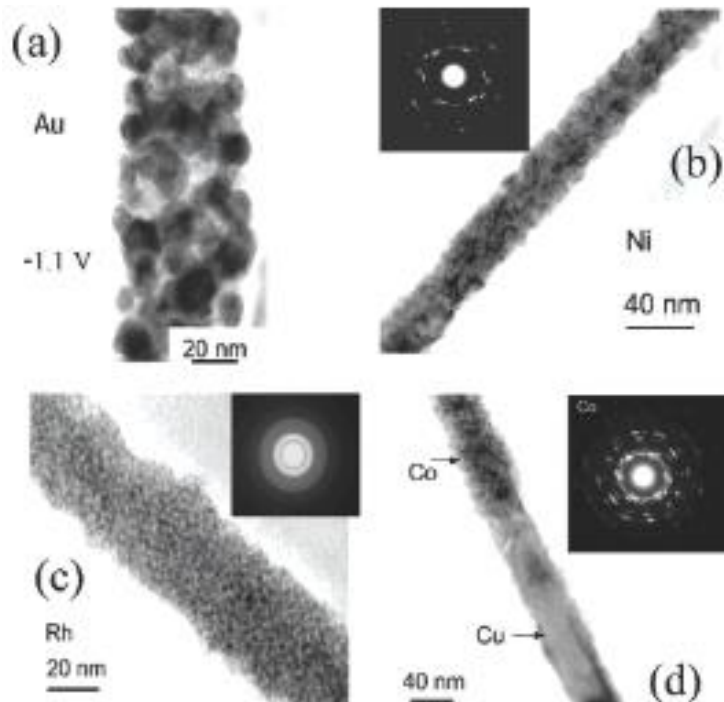
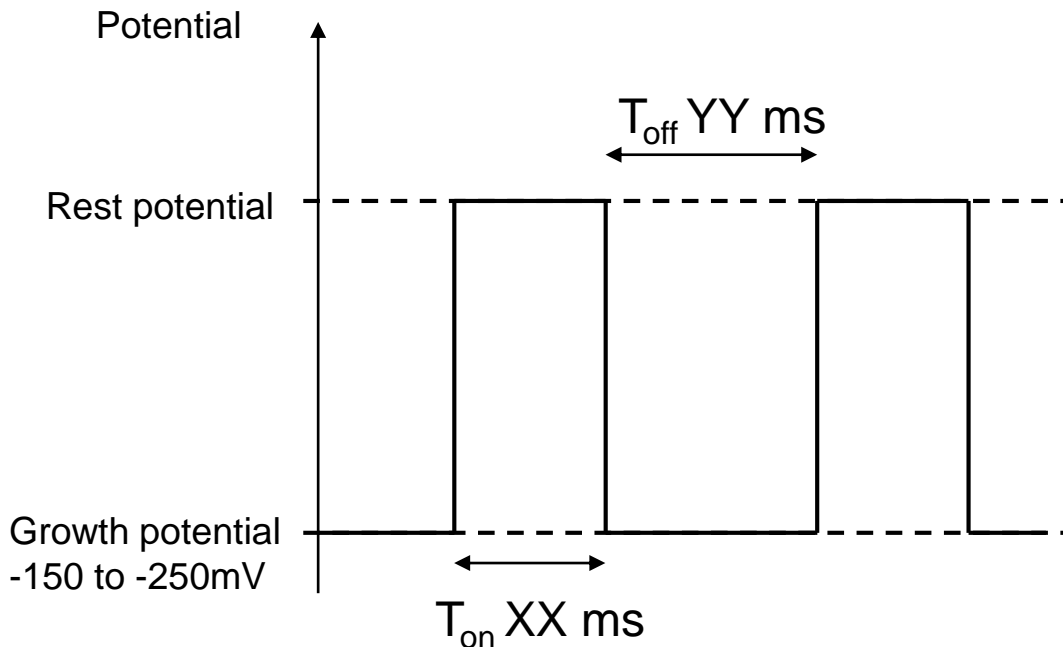


Figure 5. (a–c) TEM images of polycrystalline Au, Ni, and Rh nanowires deposited at $V_{SCE} = -1.1$, -1.1 , and -0.25 V, respectively. (d) Junction of a Co/Cu striped nanowire and the ED pattern of a Co wire; single-crystalline Cu and polycrystalline Co were deposited at -0.015 and -1.1 V, respectively. (e)

Co, Ni, Rh	Ag, Au, Cu	Pb, Sn, Bi
Temp Fusion 2700°C 3700°C	Temp Fusion 960°C 1100°C	Temp Fusion 200°C 320°C

Bi₂Te₃ nanowires

Template synthesis : Pulse electrodeposition



During the relaxation time (t_{off})

- Recovery and redistribution of the metal ion concentration at the deposition interface
- Atomic surface diffusion

Bi₂Te₃ nanowires

Template synthesis : Pulse electrodeposition

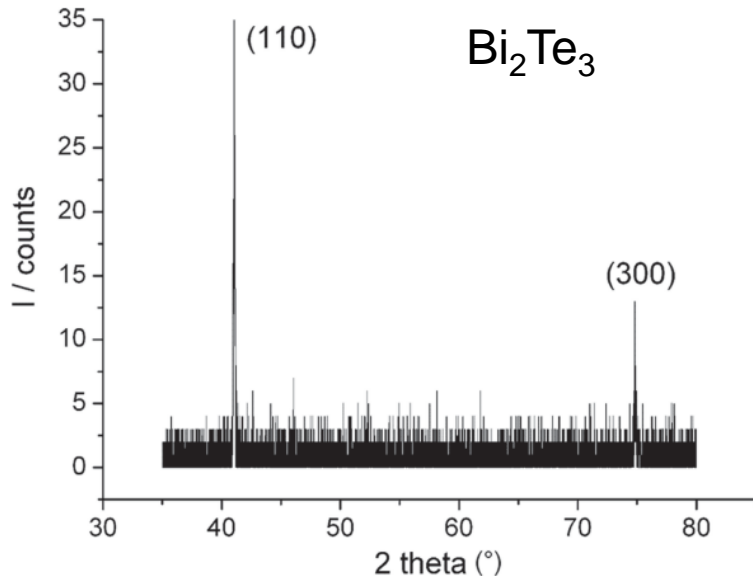


Figure 2. XRD diffraction pattern obtained on a Bi₂Te₃ nanowire array.

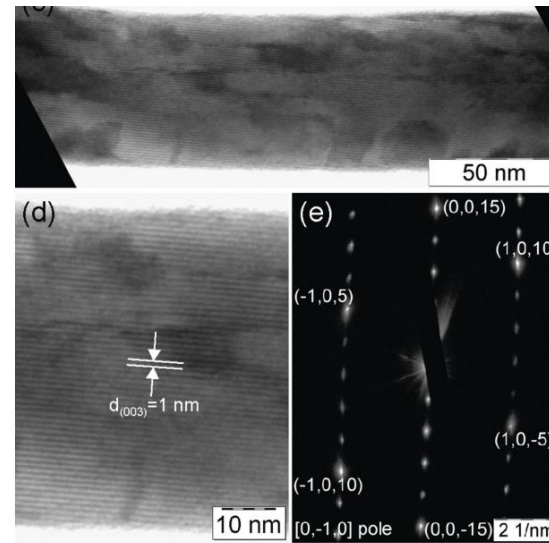
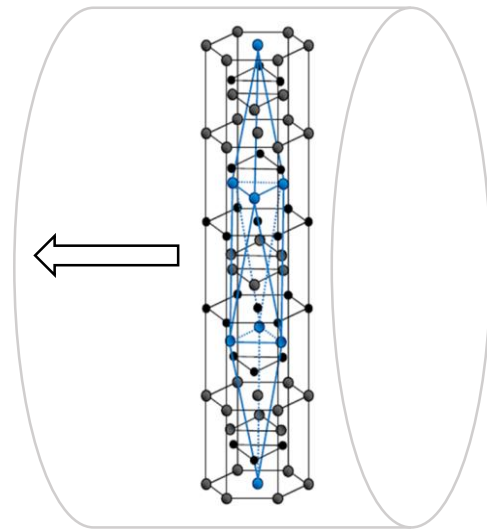


Figure 3. TEM images and electron diffraction pattern obtained in Bi₂Te₃ nanowires: a,b) Dark-field images obtained with two different {015} reflections at a sample region with five nanowires labeled 1 to 5. c-e) HRTEM images and diffraction pattern of a nanowire tilted in [0,-1,0] pole.

Growth direction



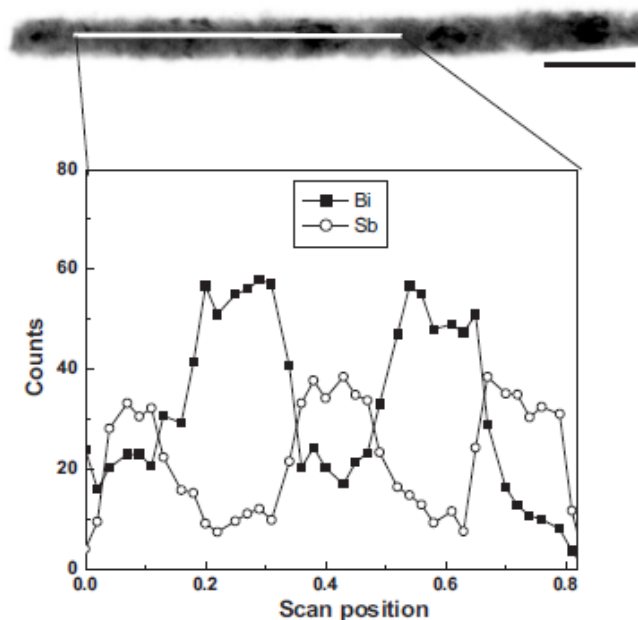
the (300) planes are almost perpendicular to the wire axis.

Orientation of c axis \perp to wire axis

Bi₂Te₃ nanowires

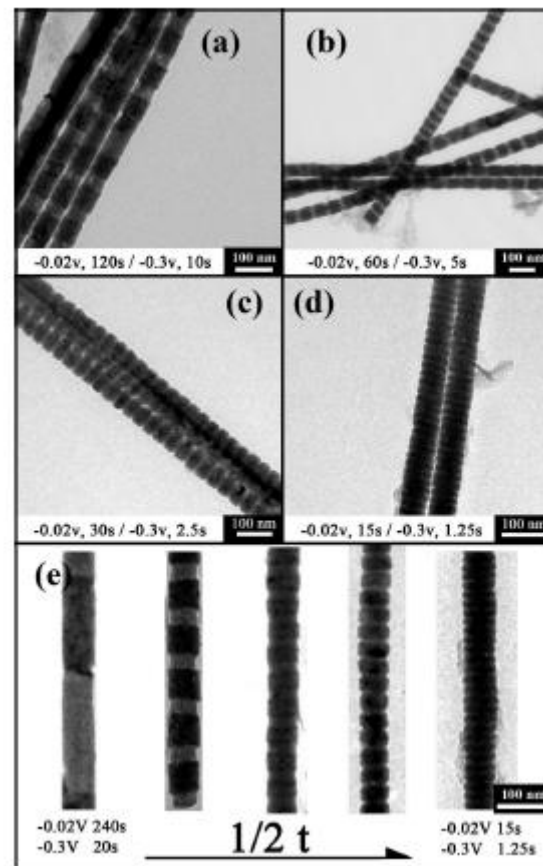
Template synthesis : Pulse electrodeposition

Pulsed deposition in PC membrane:
nanowires Bi₂Te₃/(Bi_{0.3}Sb_{0.7})₂Te₃ from a
unique solution by adjusting potentials



2007 Yoo *Advanced Mater.*
2008 Wang *J. Phys. Chem. C.*

Pulsed deposition in AAM :
nanowire Bi₂Te₃/Sb
min period: 10 nm



Electrodeposition of nanostructures

- ✓ **Geometrical engineering
at nanoscale**

Large panel of nanostructures : 2D, nanowires, core@shell
nanowires, modulated nanowires, nanotubes

- ✓ **Low cost synthesis (low temperature, absence of vacuum,
no advanced equipment**

- ✓ ***Specific electrochemical systems***

Electrodeposition requires to combine
electrochemical analysis and a materials science approach

Electrosynthesis of nanostructures for energy

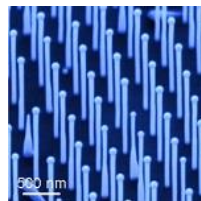
N. STEIN

Electrochemistry of Materials Research Group

thematic school of the GDR NAME

*ELaboration of NANOmaterials for the recovery, conversion,
transport and storage of energy*

11-16 June 2023



N A M E

GDR NANoMaterials for Energy applications